

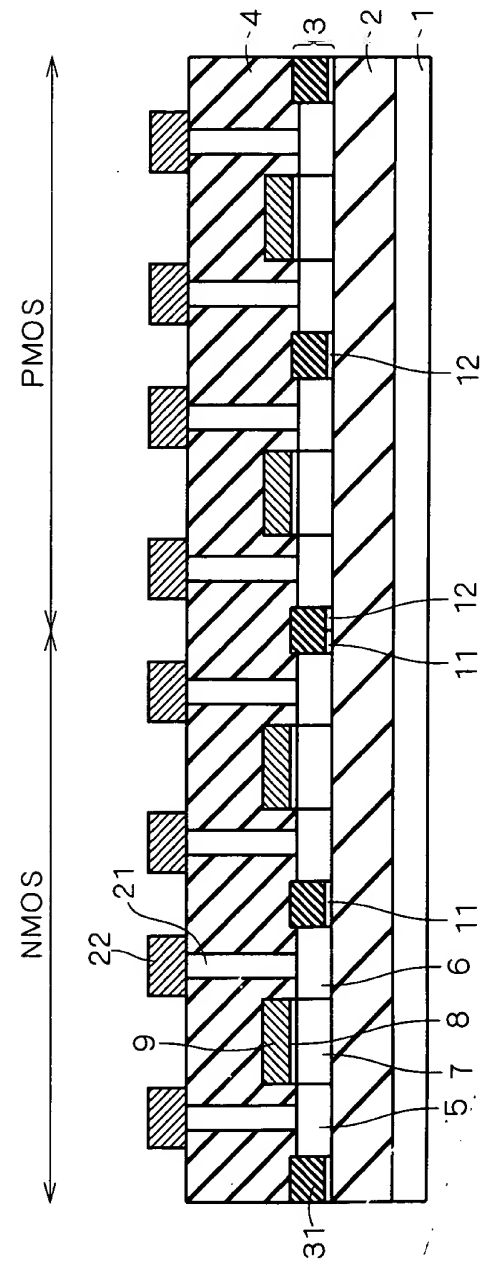
650227-4E69460

257
446

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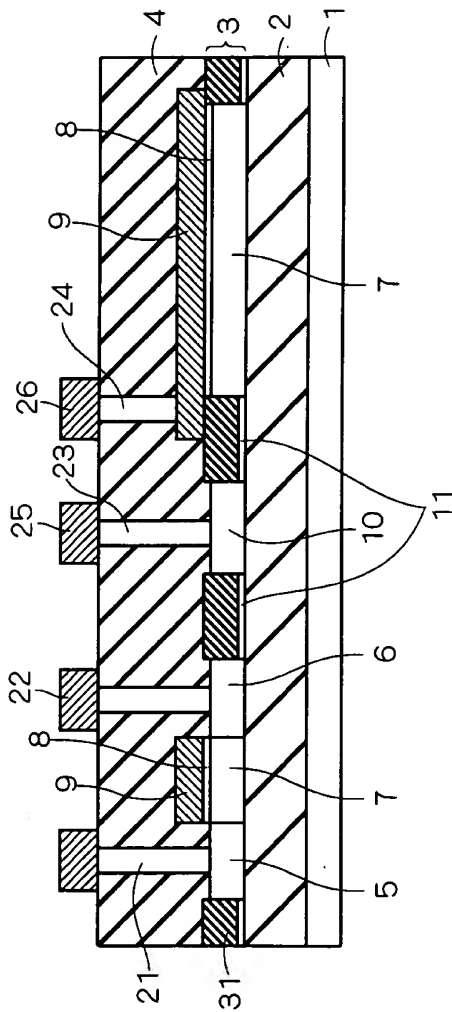
159

FIG. 1



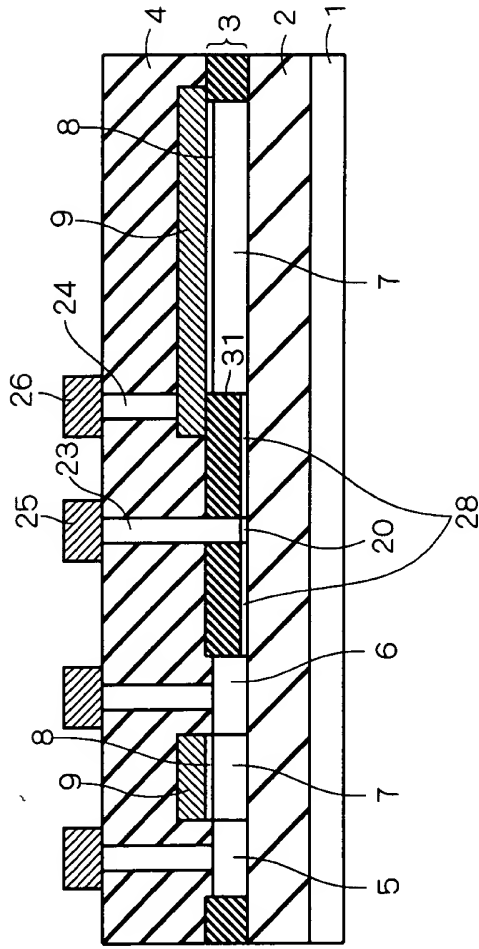
102
102/102

FIG. 2



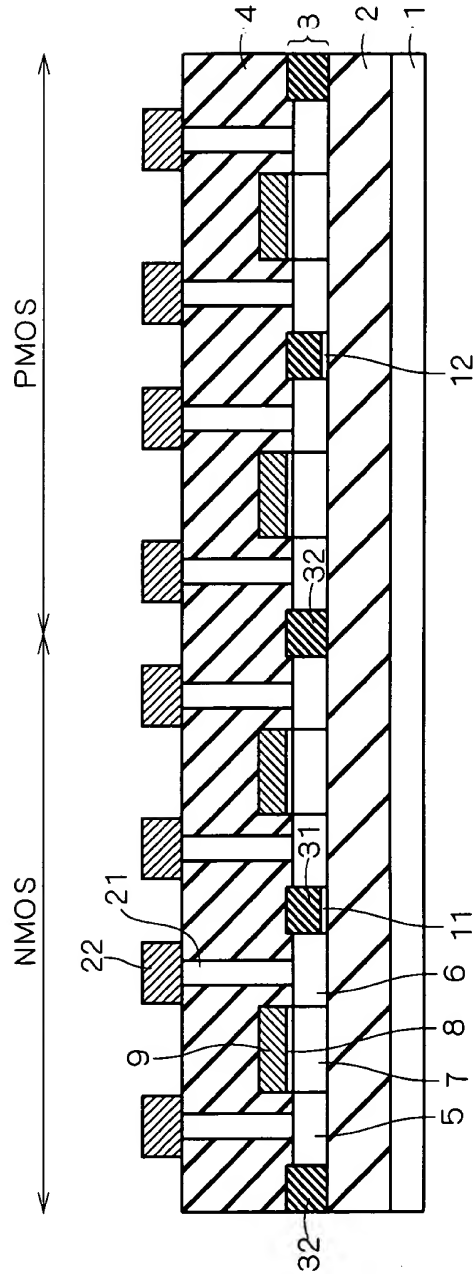
660227 42599460

FIG. 4



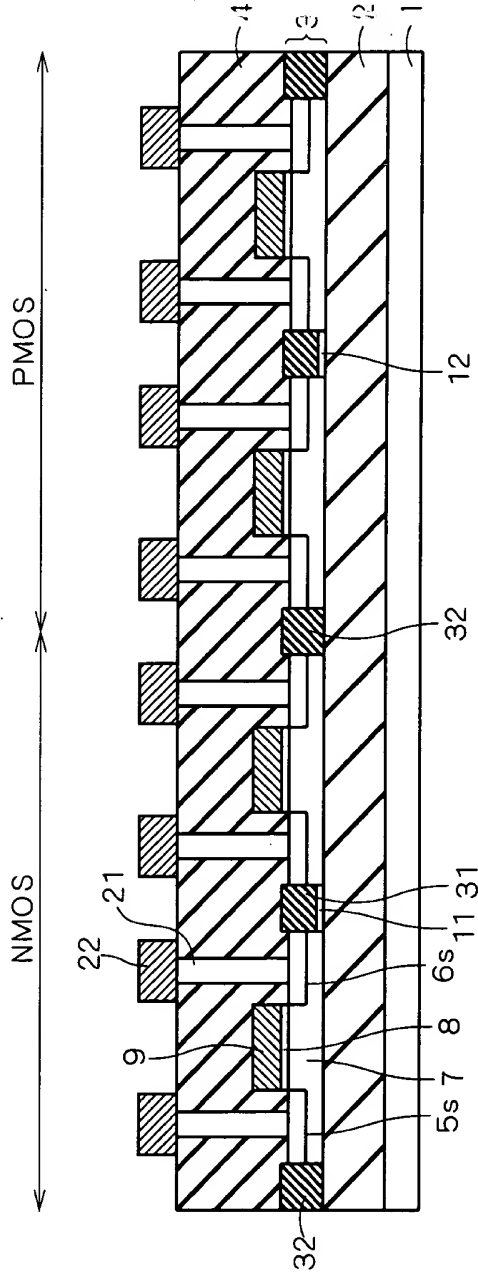
660227-4E699450

FIG. 5



660227-4E599460

FIG. 6



35

This diagram shows a cross-sectional view of a semiconductor device. It is divided into two main sections: NMOS on the left and PMOS on the right, indicated by double-headed arrows at the top. The device consists of a substrate (1) with a gate oxide layer (2). A gate stack (3) is formed on the surface. The NMOS region features a channel layer (4) and a source/drain region (5). The PMOS region features a channel layer (6) and a source/drain region (7). A central region (8) is also shown. Various layers and structures are labeled with numbers 1 through 12, 21, 22, 29, 31, 33, and 34.

FIG. 8

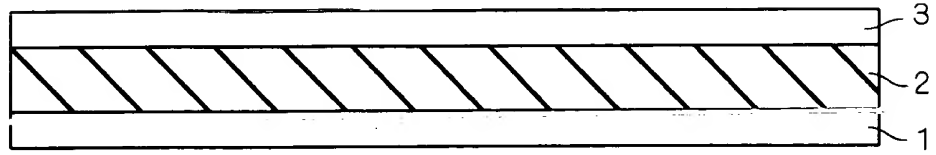


FIG. 9

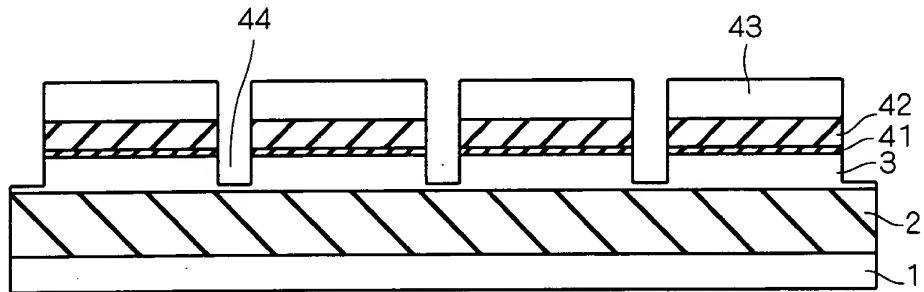


FIG. 10

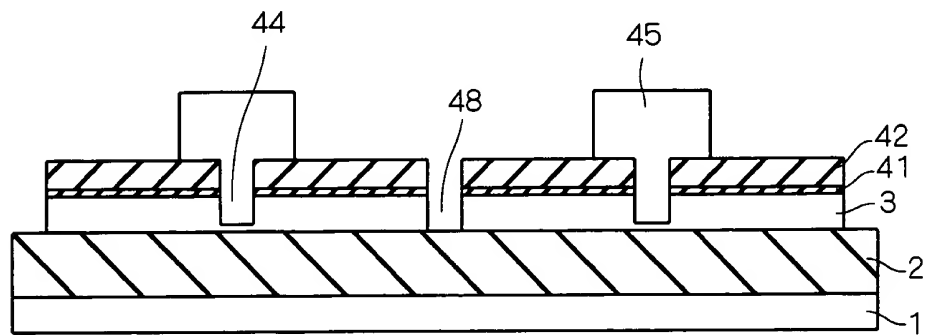


FIG. 11

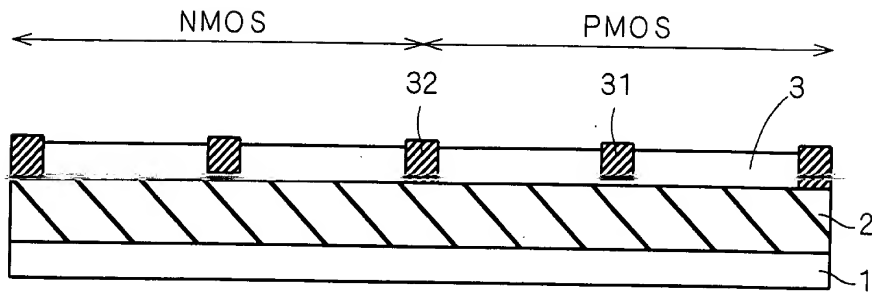


FIG. 12

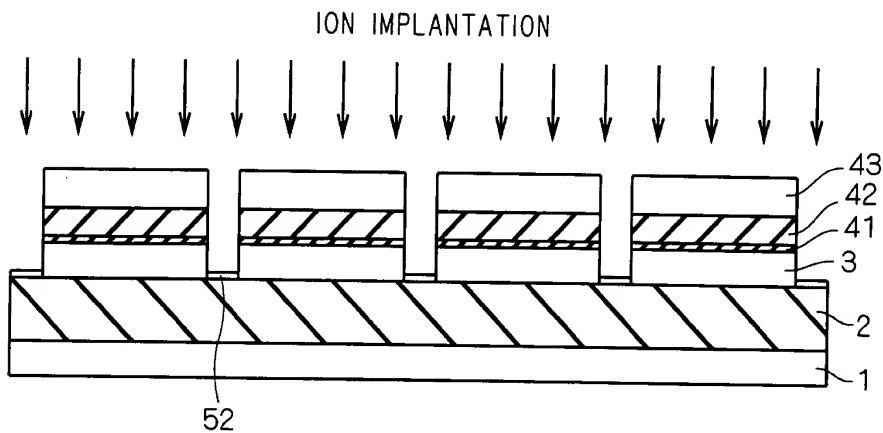


FIG. 13

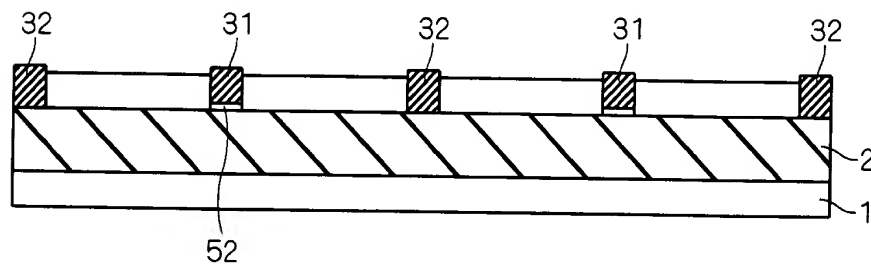
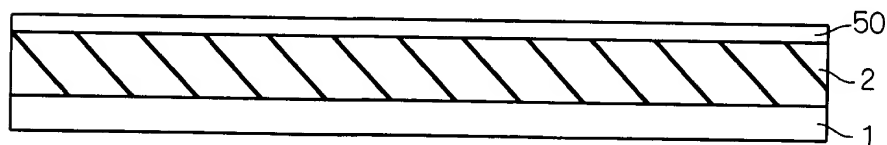


FIG. 14



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FIG. 15

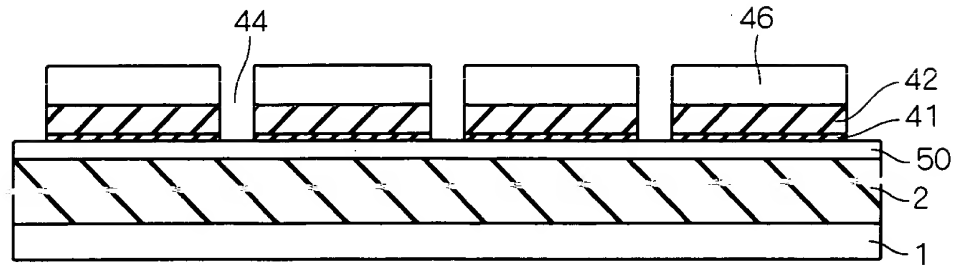


FIG. 16

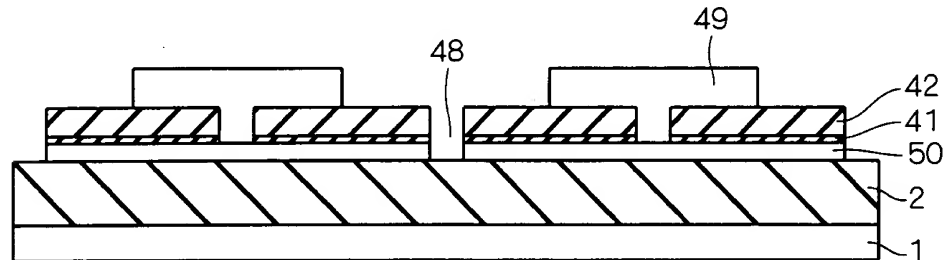


FIG. 17

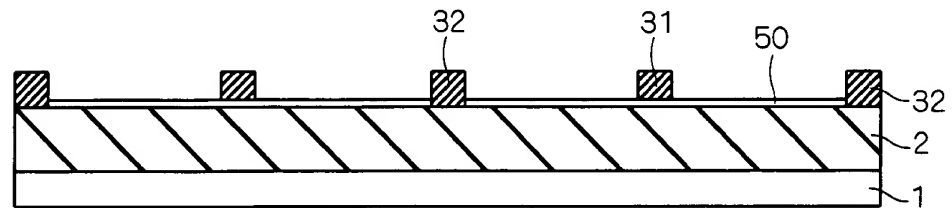
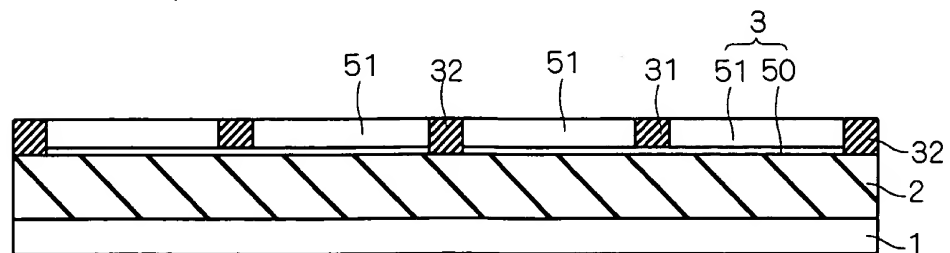


FIG. 18



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FIG. 19

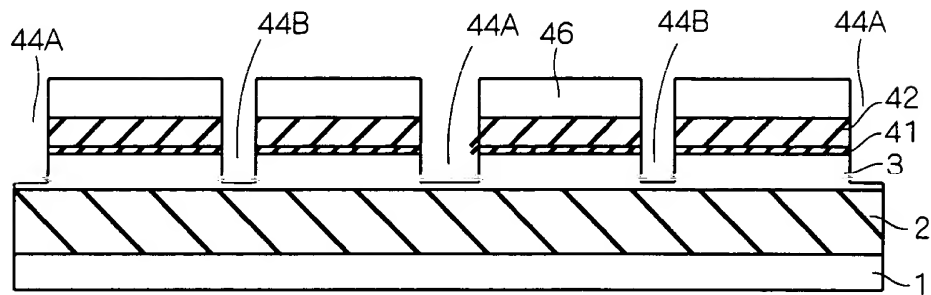


FIG. 20

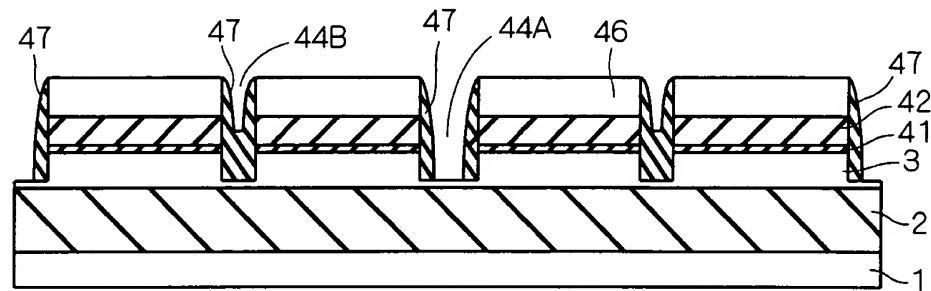


FIG. 21

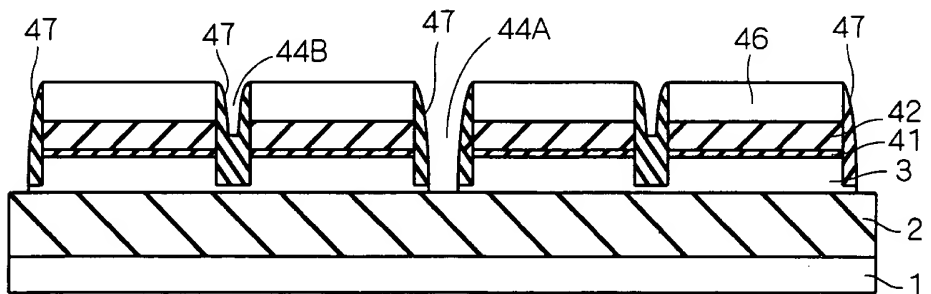


FIG. 22

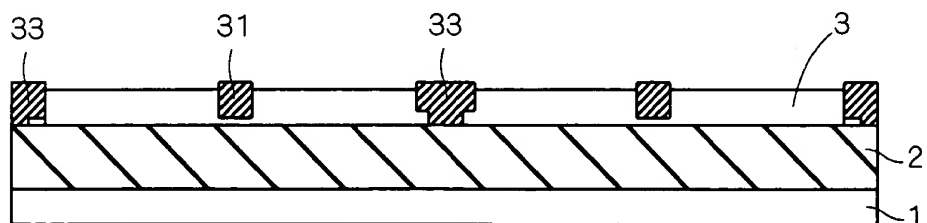


FIG. 23
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FIG. 23

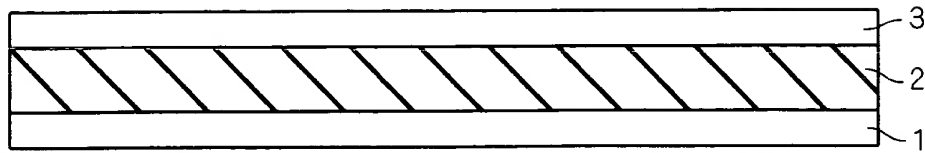


FIG. 24

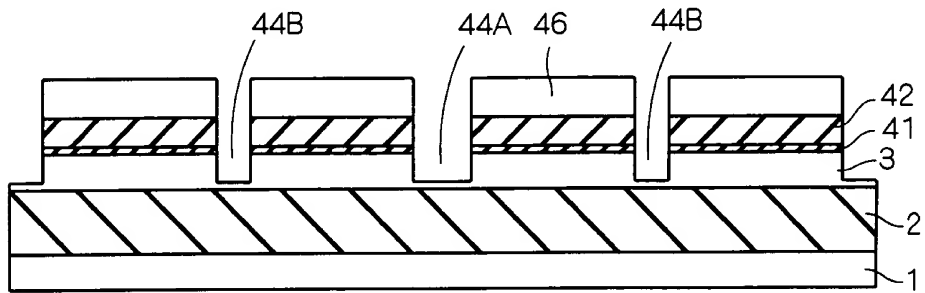


FIG. 25

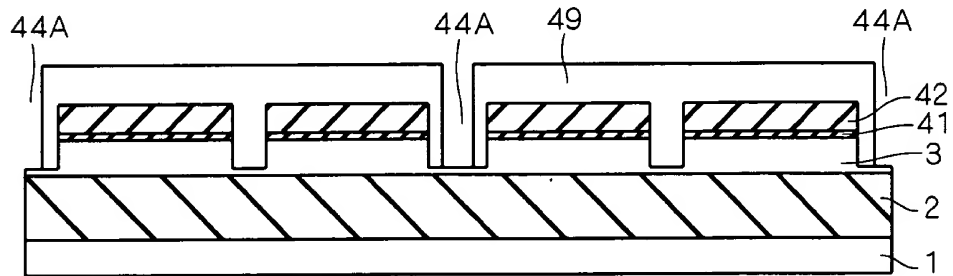
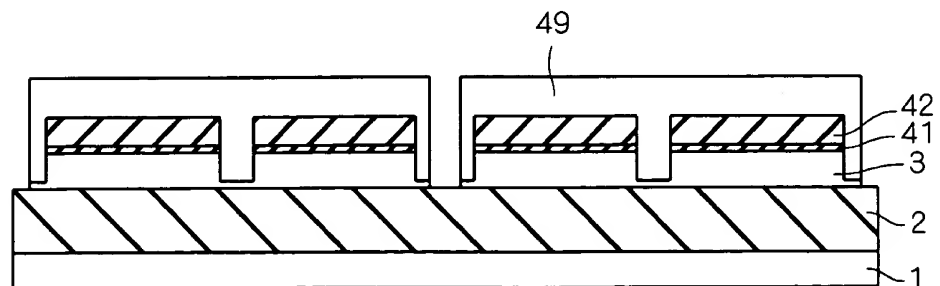
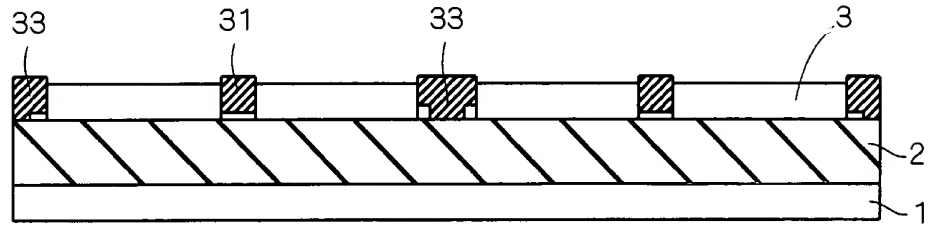


FIG. 26



0945634-12099
660227-4269460

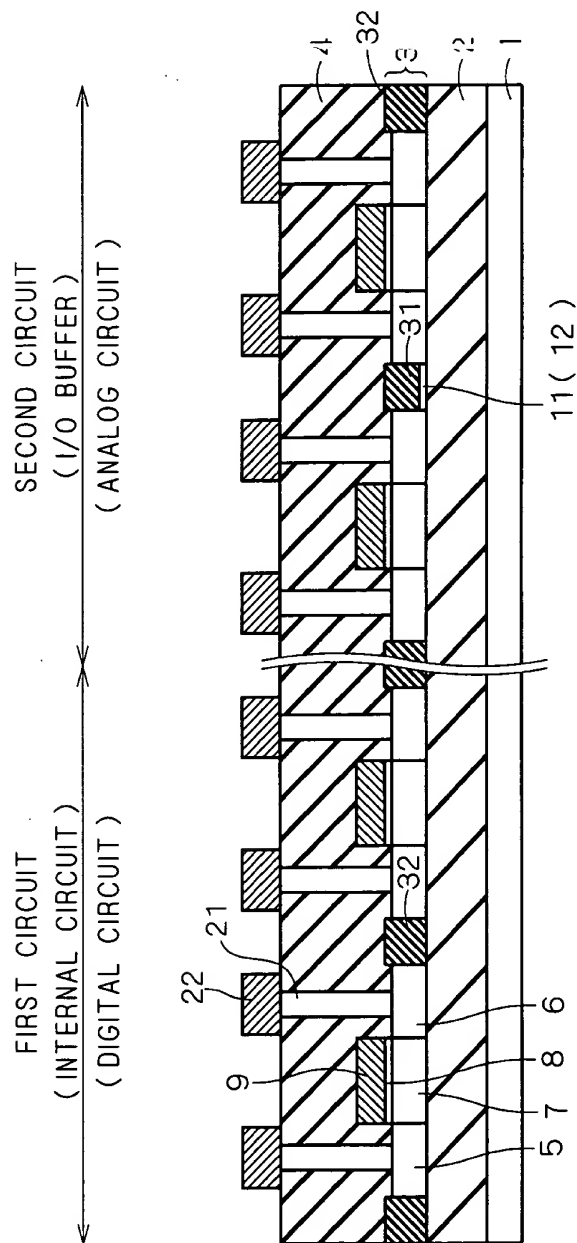
FIG. 27



0346594-12009
600227-1659450

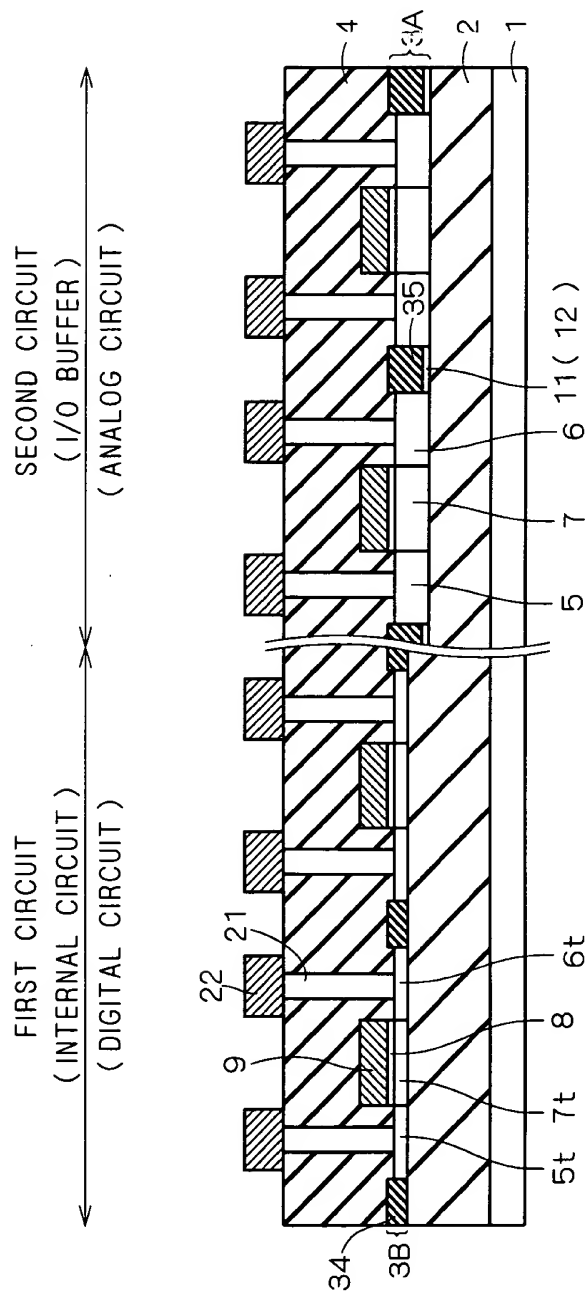
SECRET

FIG. 28



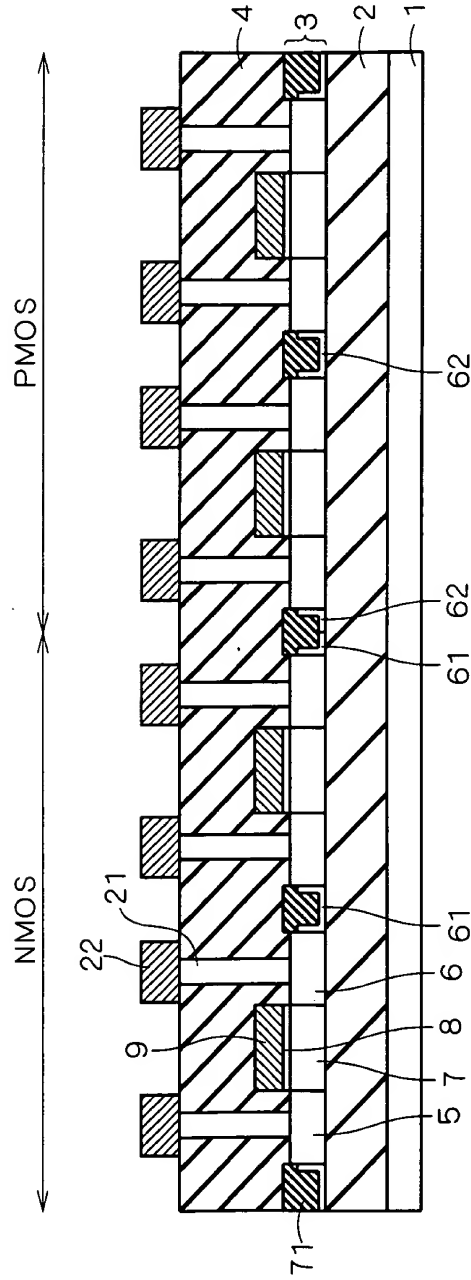
660227 4699460

FIG. 29



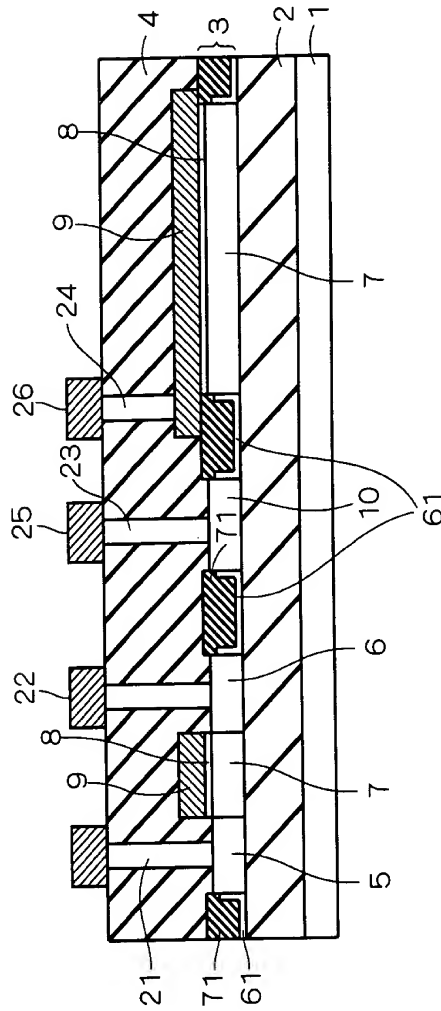
660227-4E69460

FIG. 30



6602227-1699450

FIG. 31



Sheet 18 of 18

FIG. 32

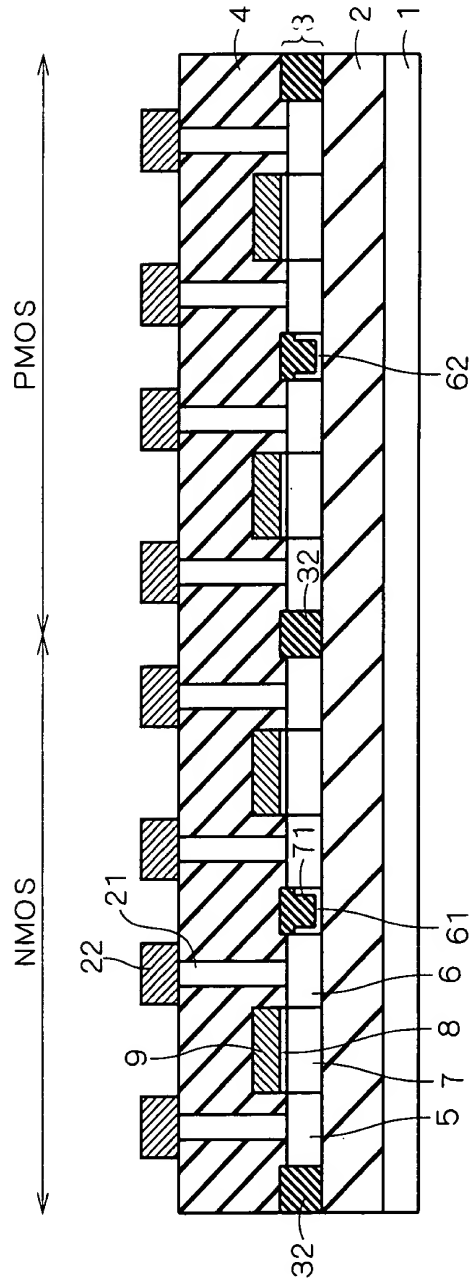


FIG. 33

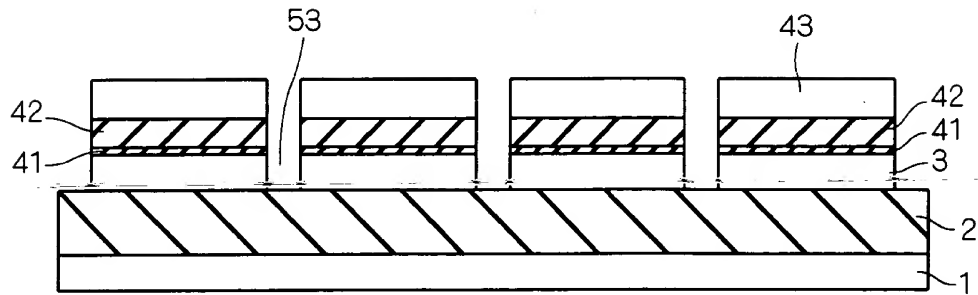


FIG. 34

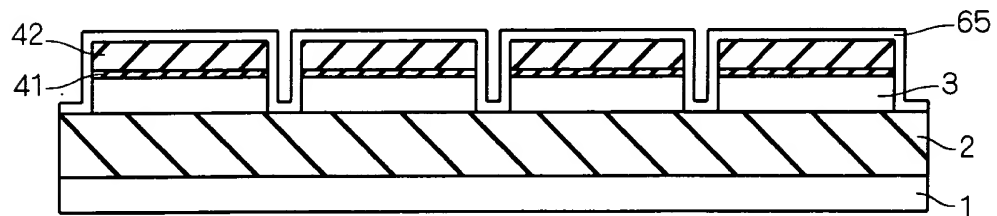


FIG. 35

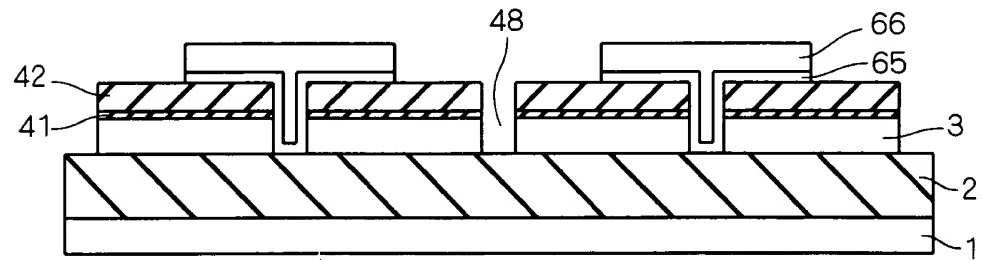


FIG. 36

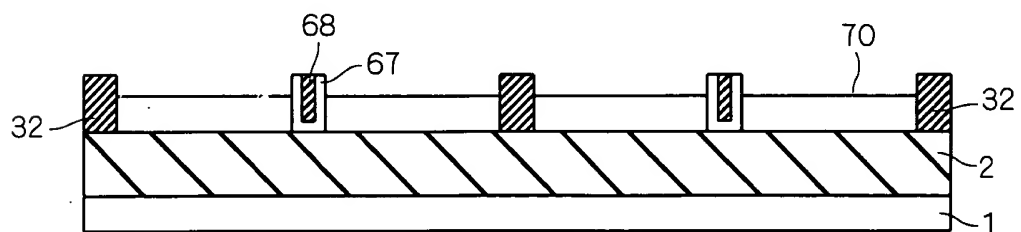


FIG. 37

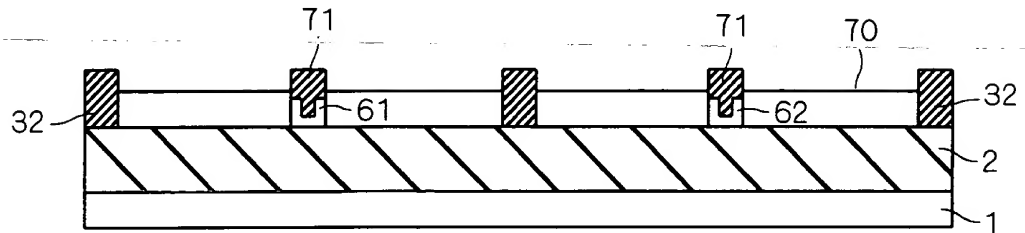


FIG. 38

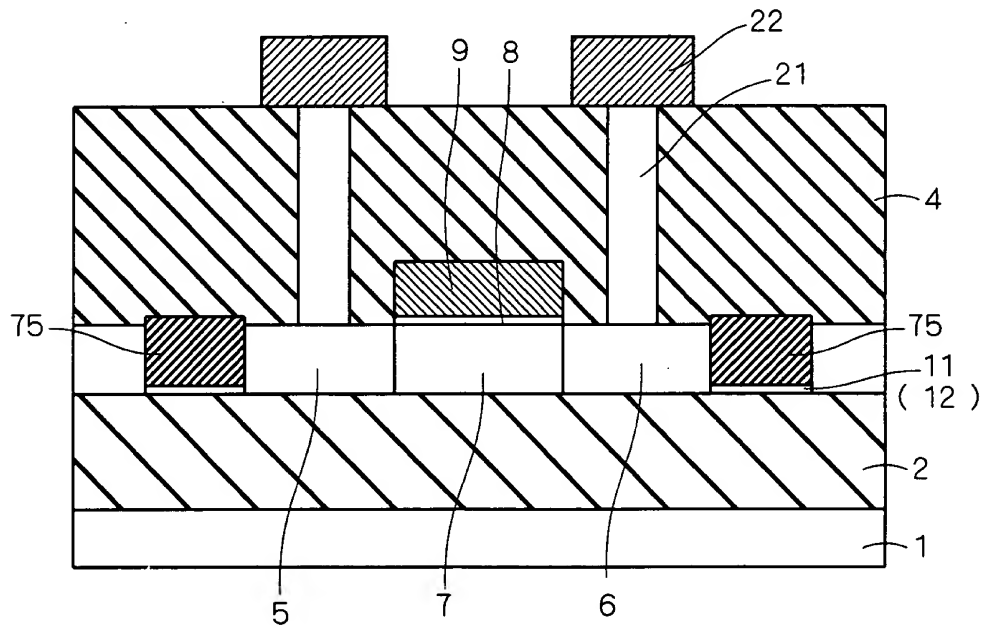


FIG. 39

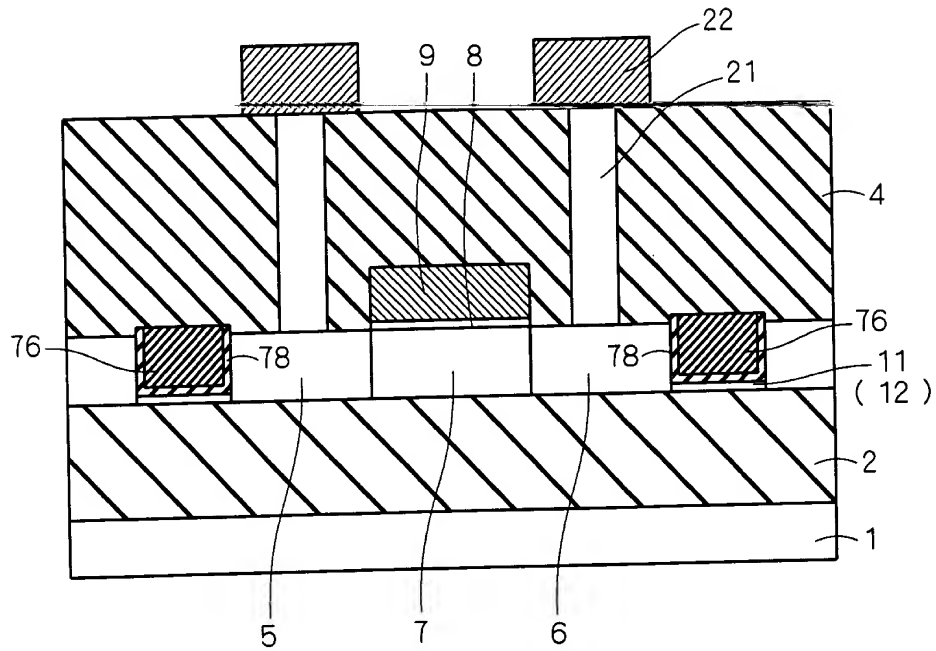
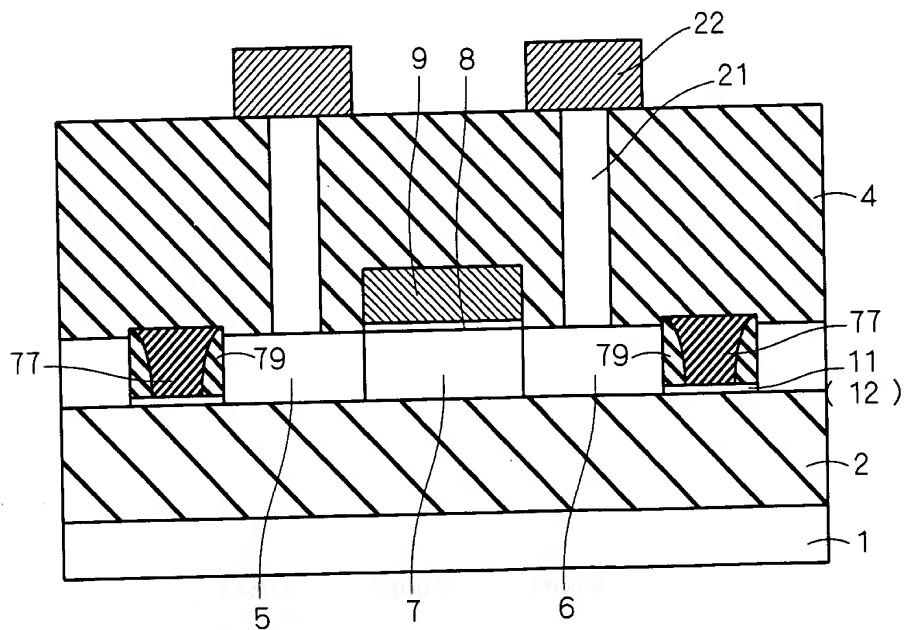
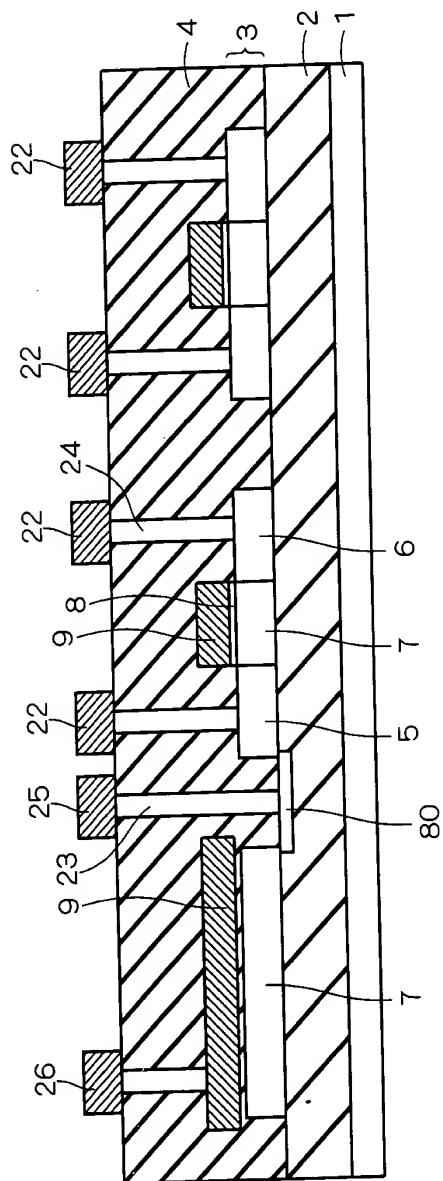


FIG. 40



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FIG. 41



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FIG. 42

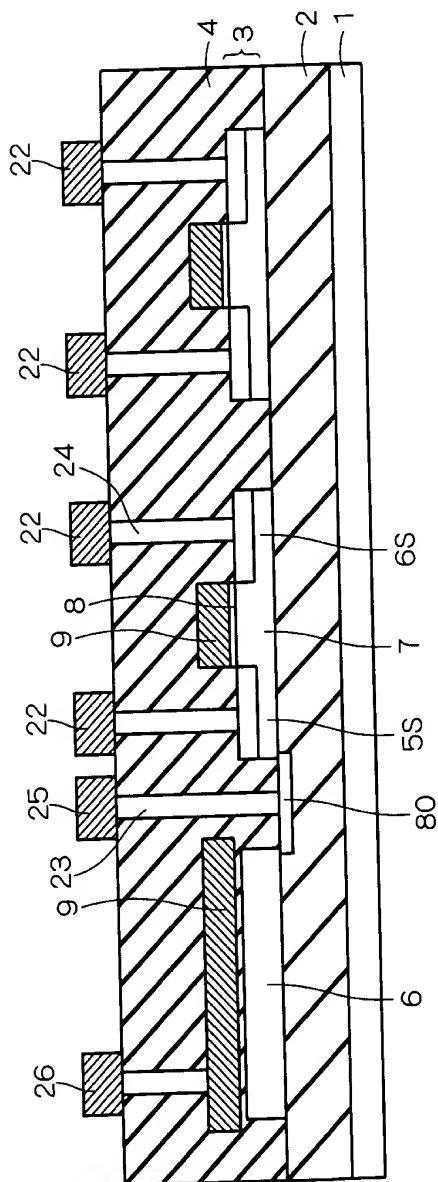


FIG. 43

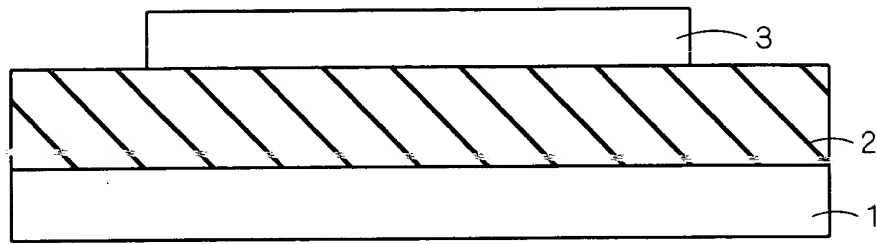


FIG. 44

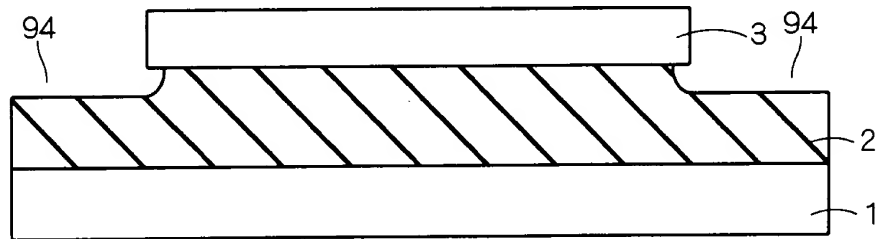


FIG. 45

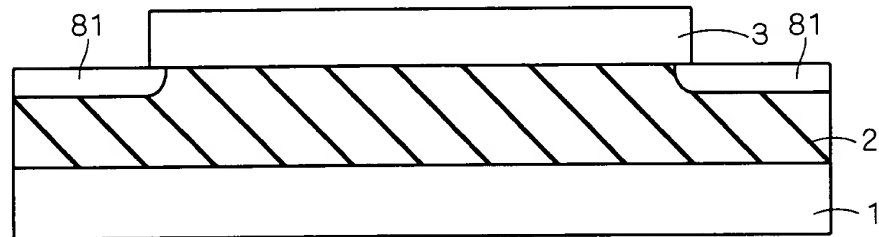


FIG. 46

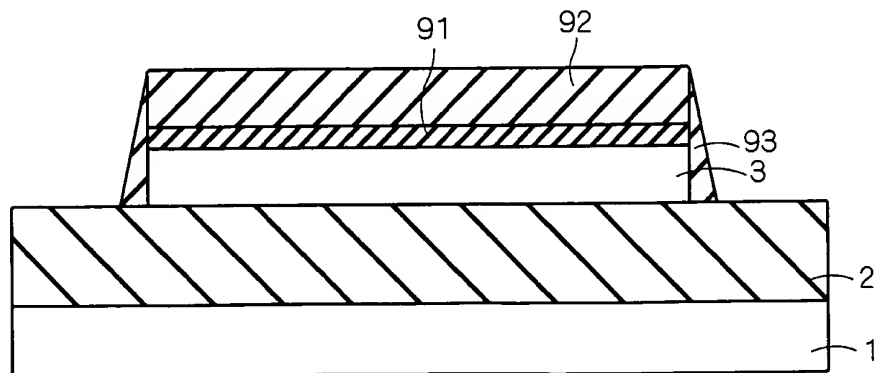


FIG. 47

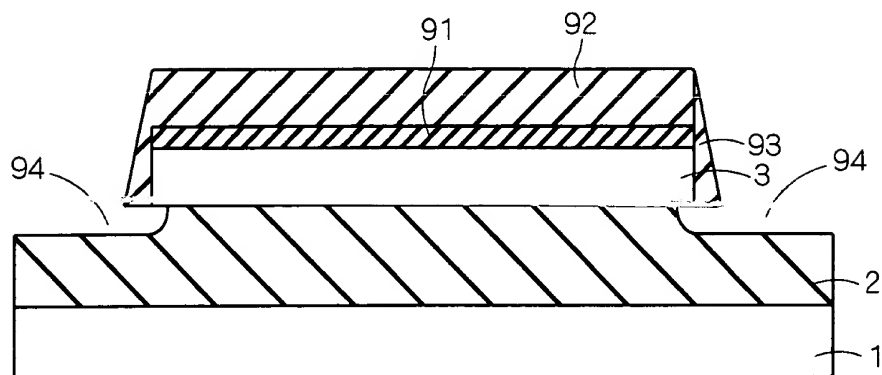


FIG. 48

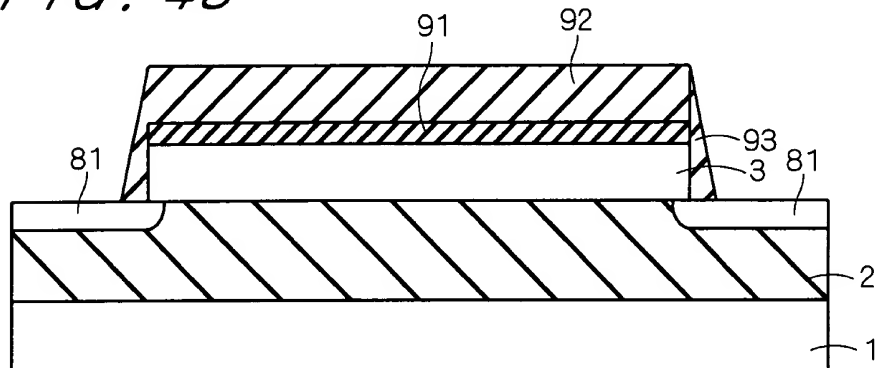
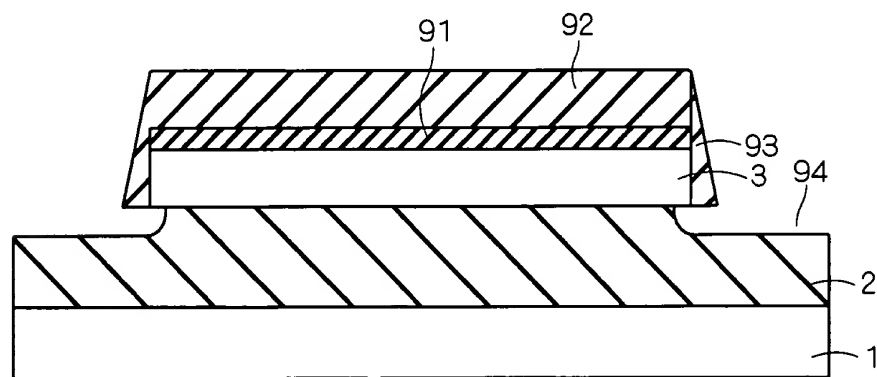
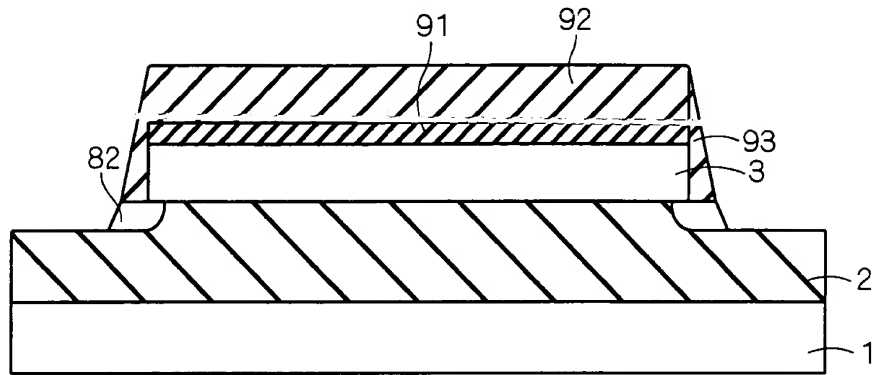
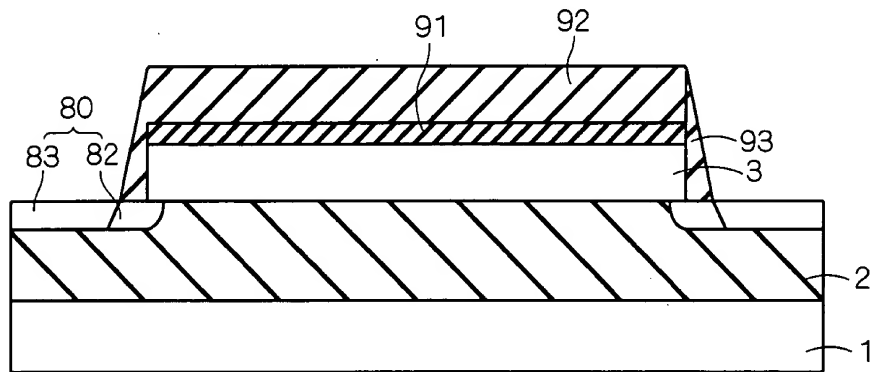


FIG. 49

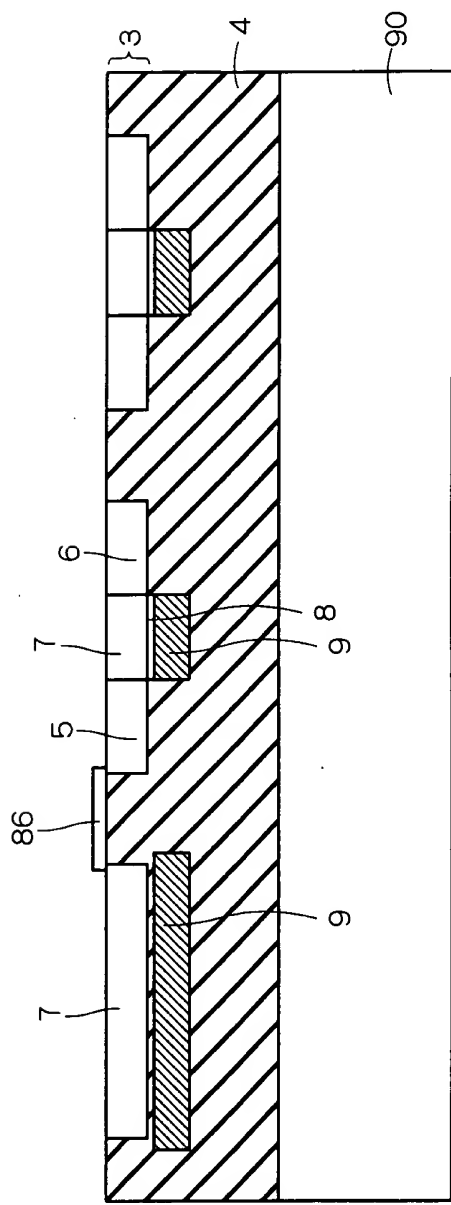


660221-42639460

FIG. 50*FIG. 51*094694-12009
660221-4E699460

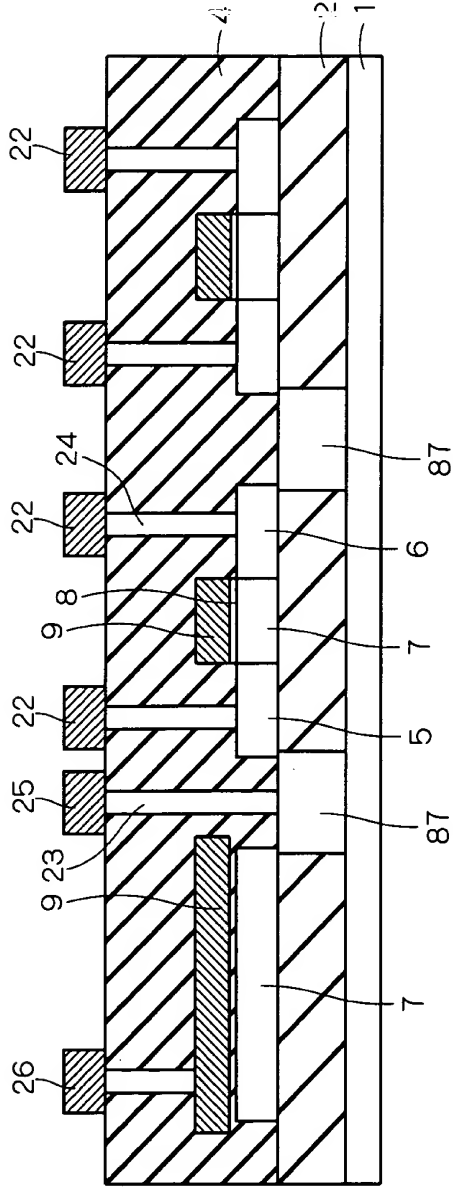
Sheet 27 of 59

FIG. 52



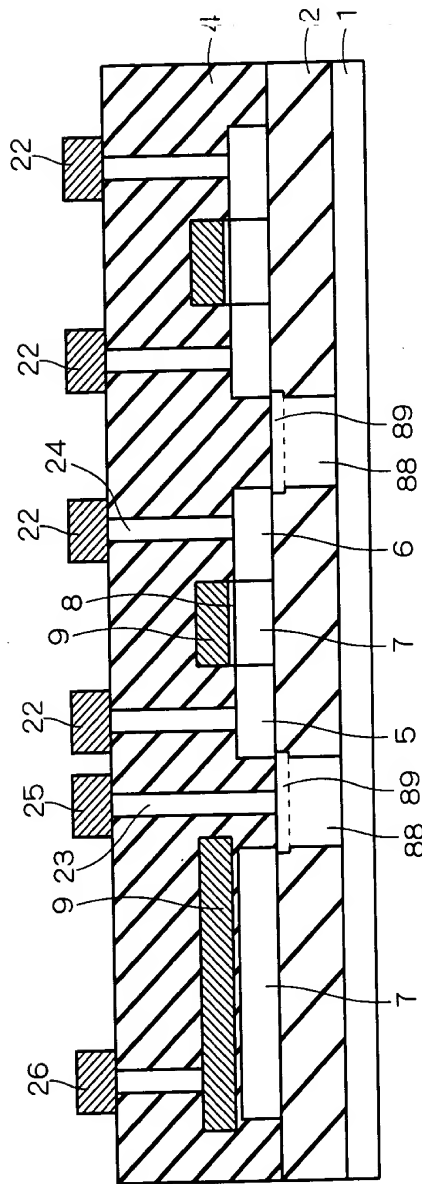
660227-HE699450

FIG. 53



660221-1263460

FIG. 54



660224-1E639460

FIG. 55

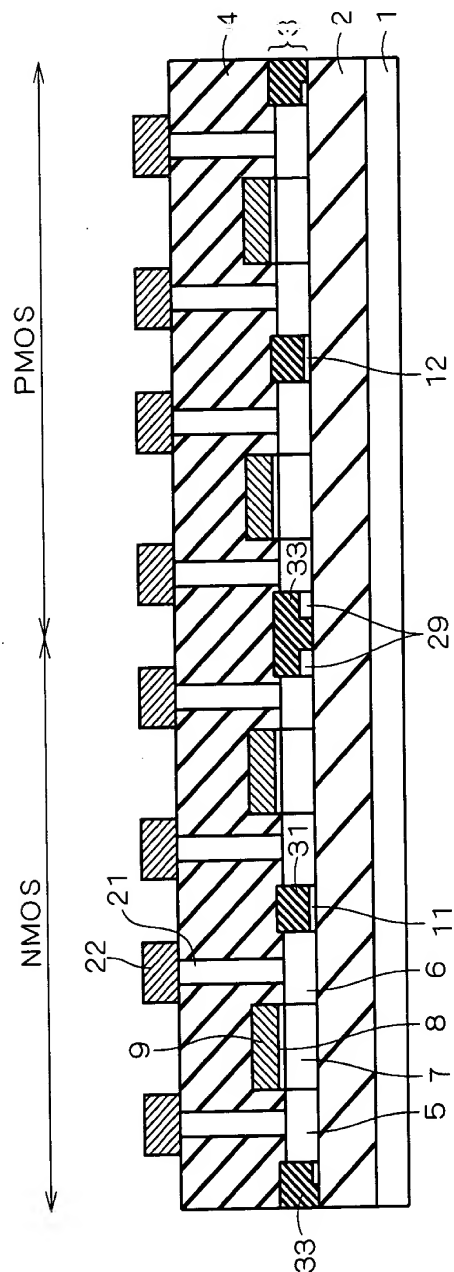


FIG. 56

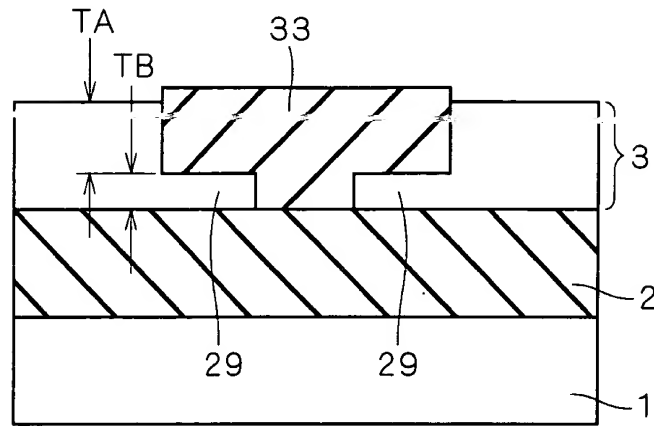


FIG. 57

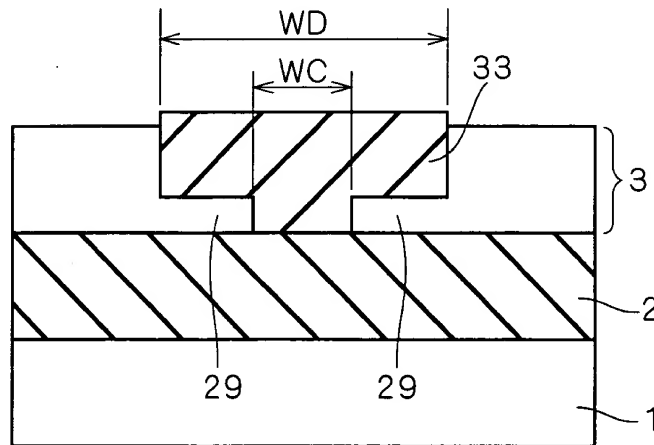


FIG. 58

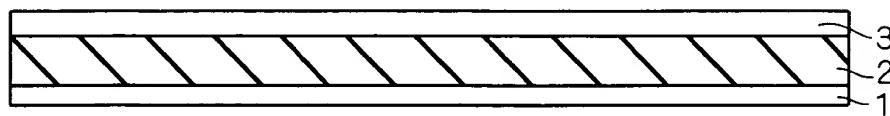


FIG. 59

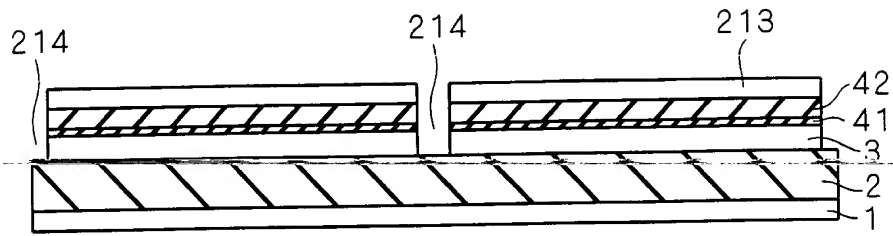


FIG. 60

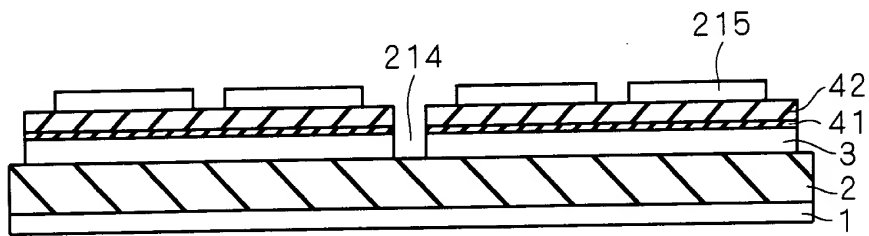


FIG. 61

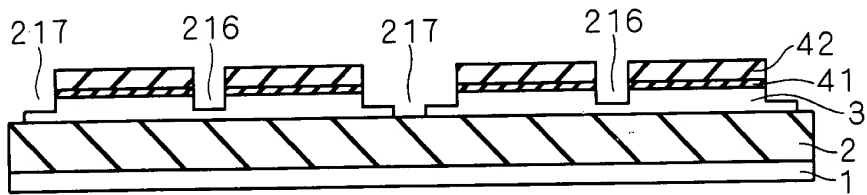
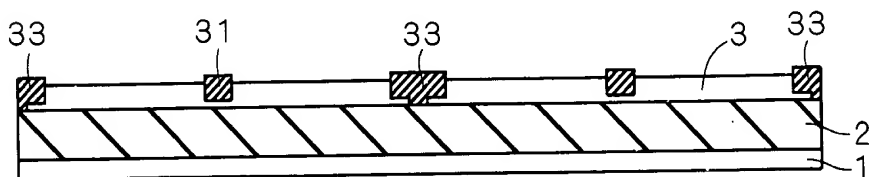


FIG. 62



660227-11693450

FIG. 63

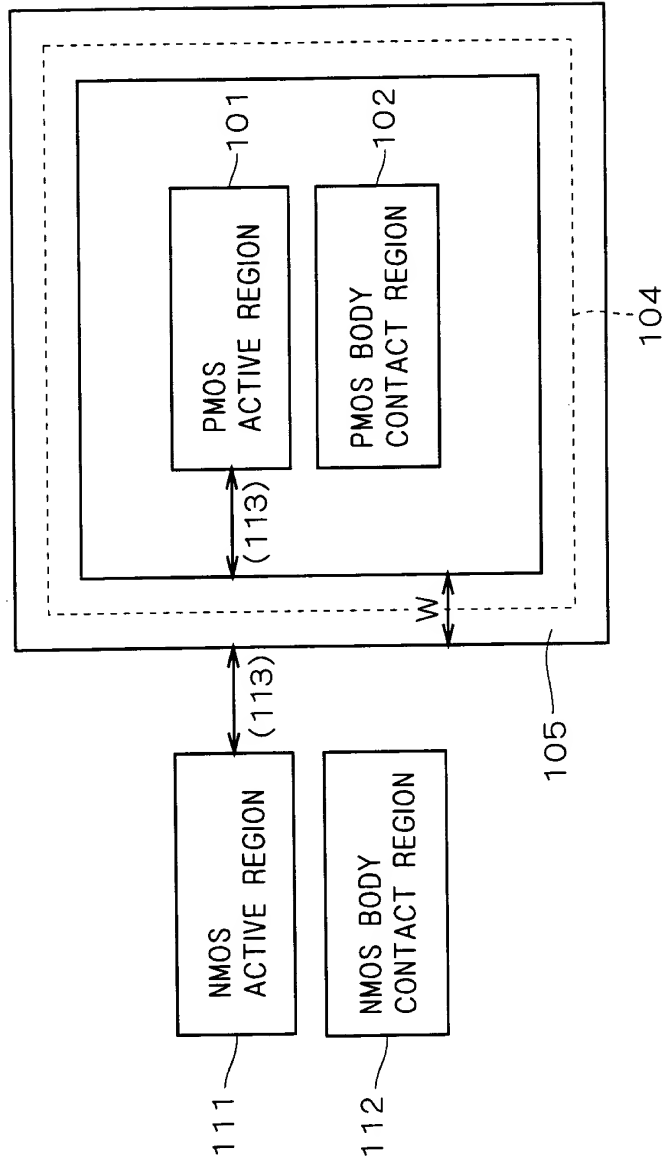


FIG. 64

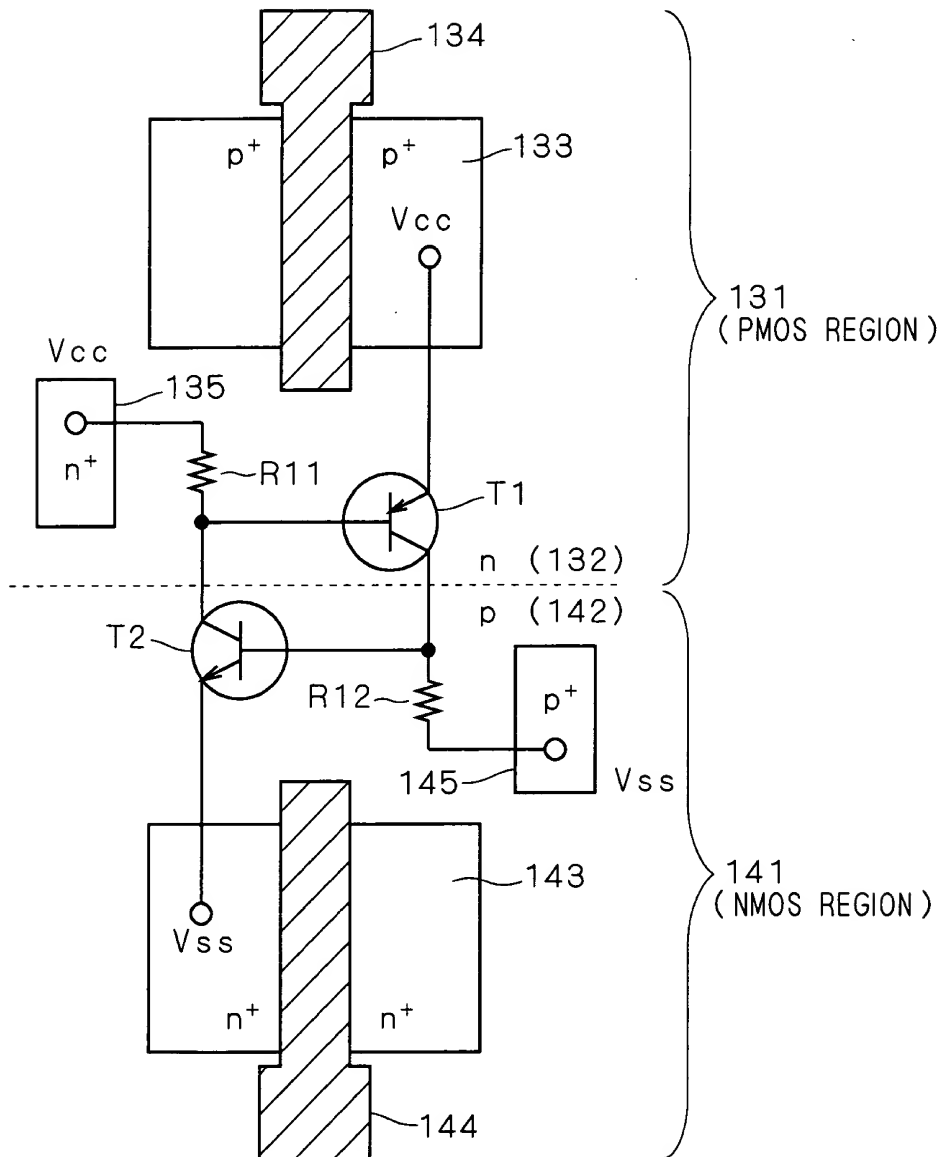


FIG. 65

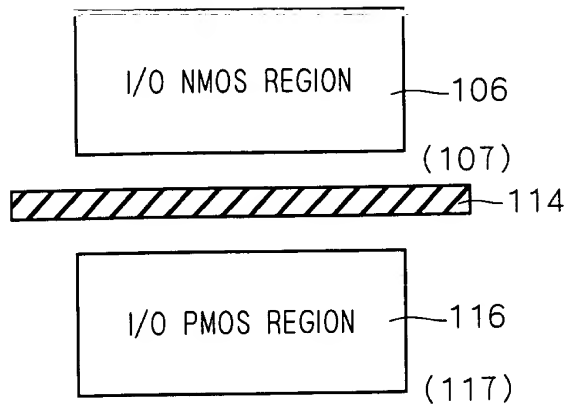


FIG. 66

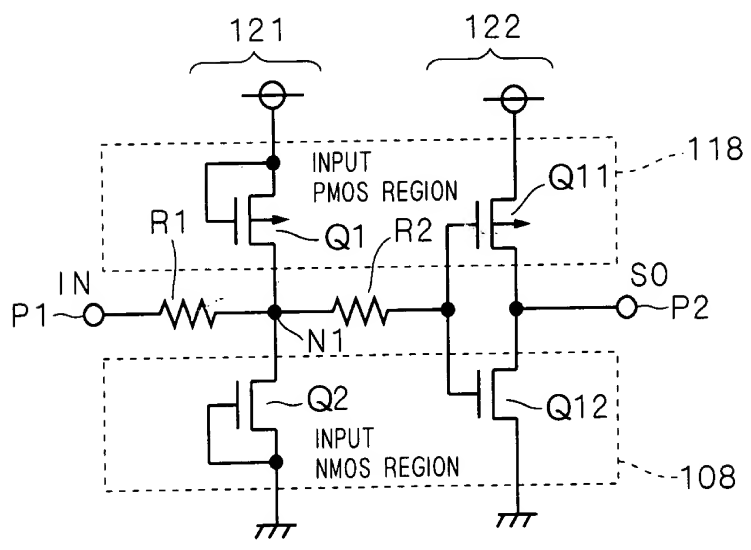


FIG. 67

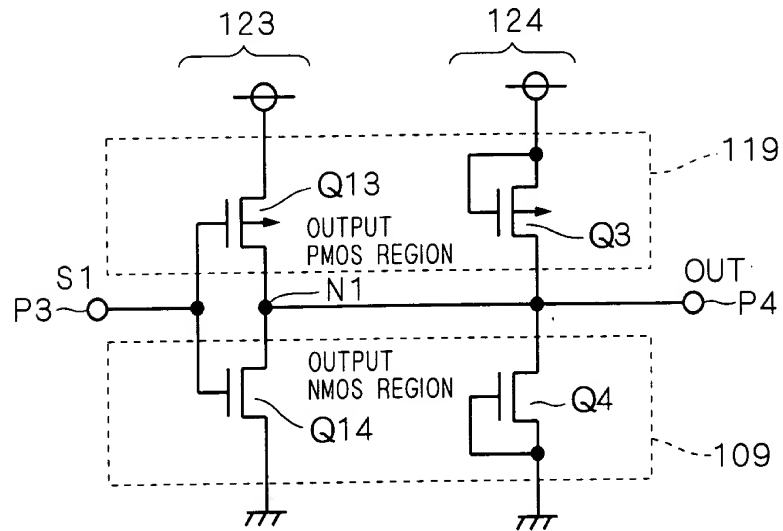


FIG. 68

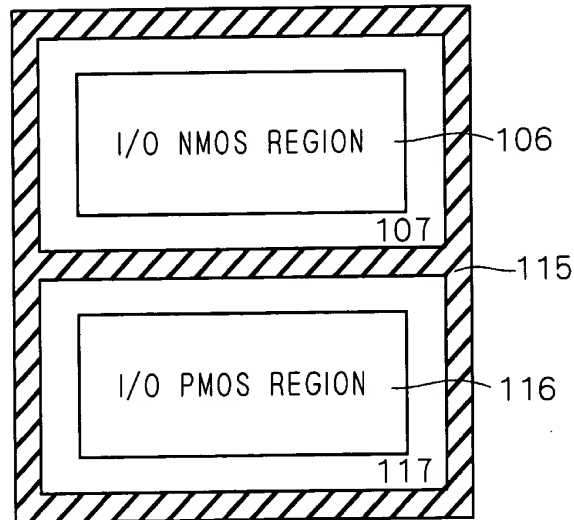


FIG. 69

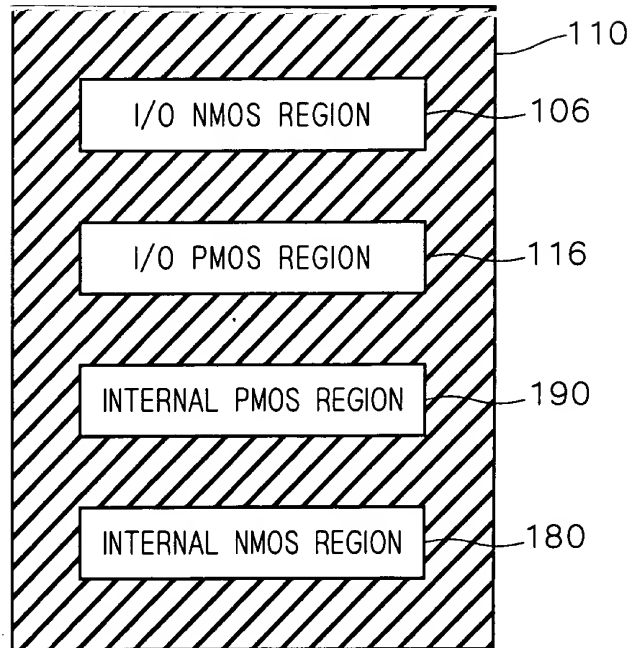


FIG. 70

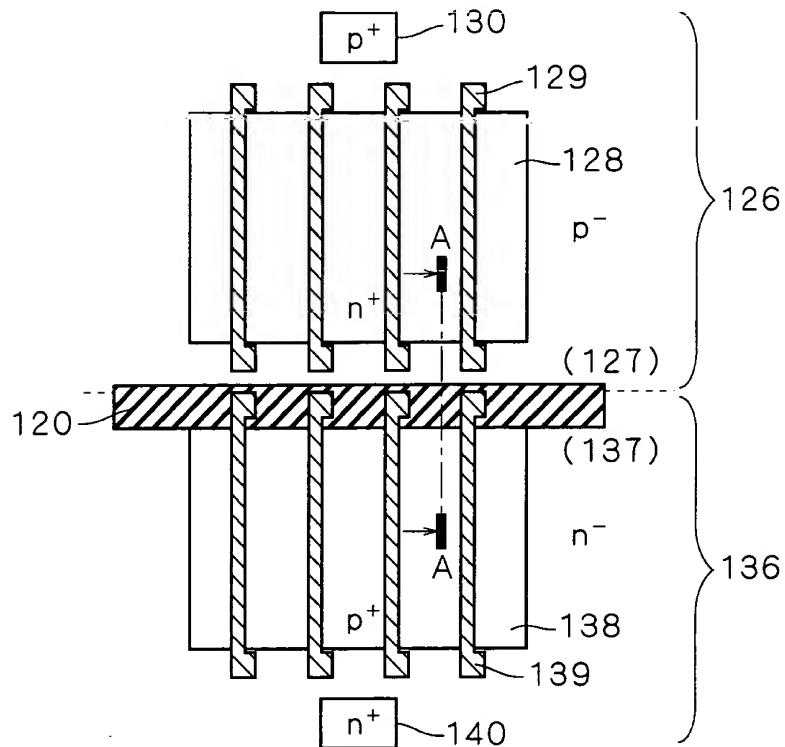


FIG. 71

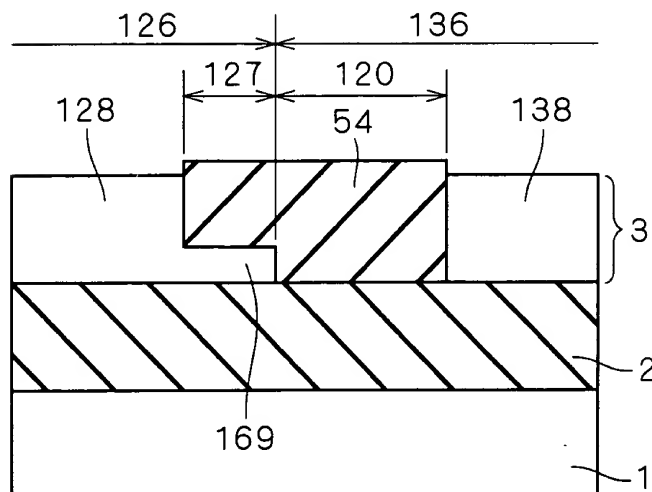


FIG. 72

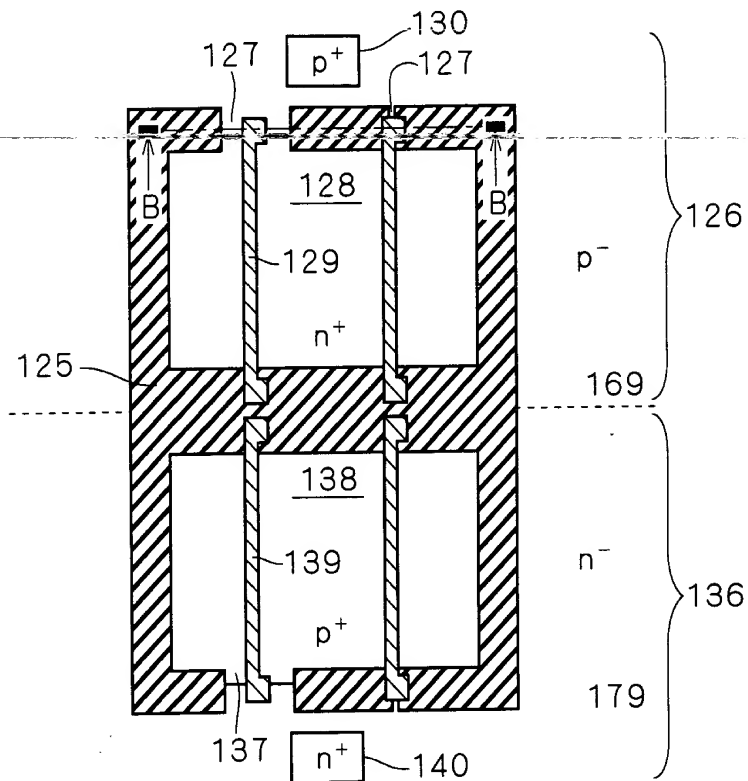


FIG. 73

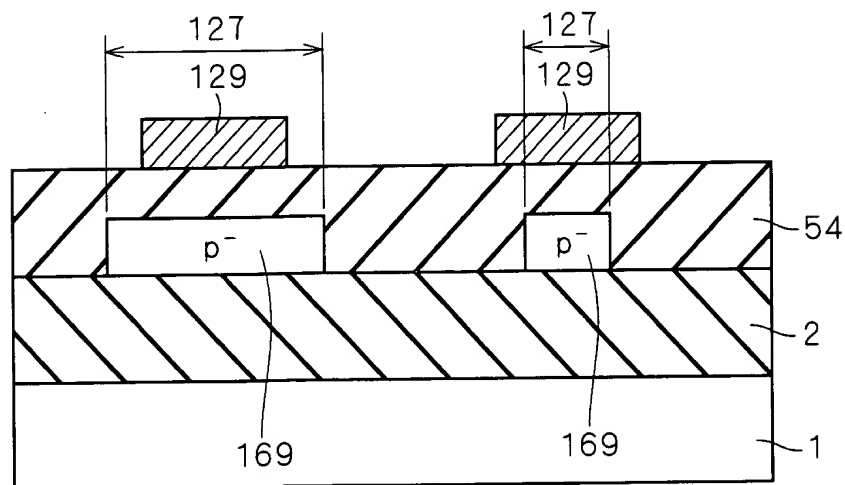
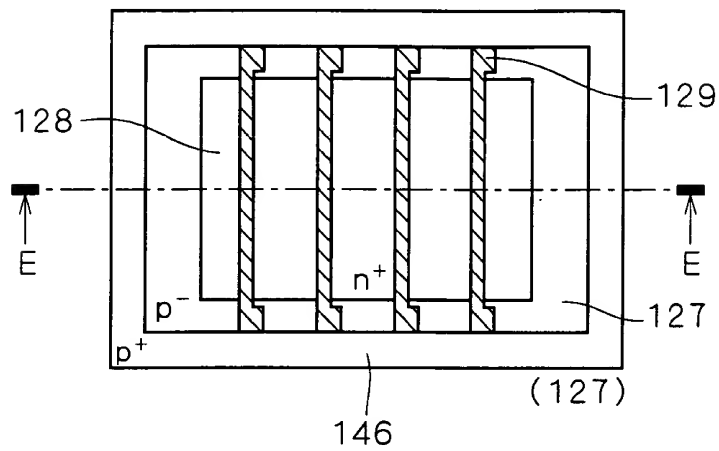


FIG. 74



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FIG.	
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FIG. 75

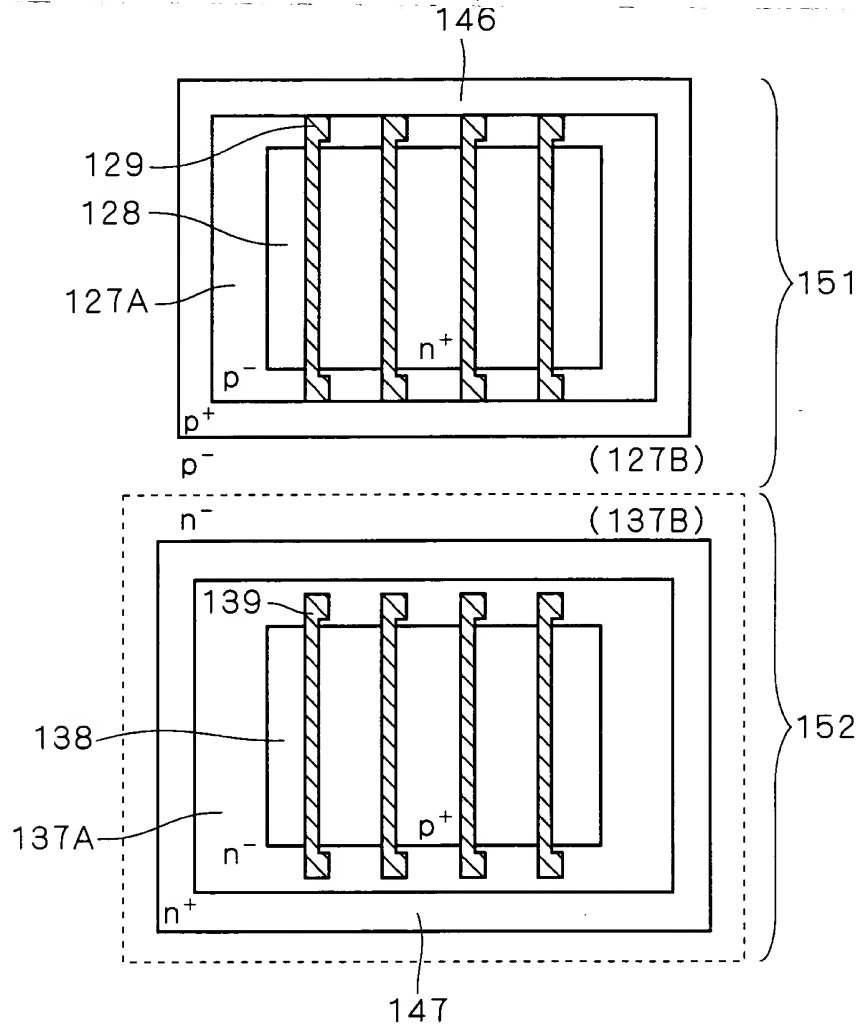


FIG. 76

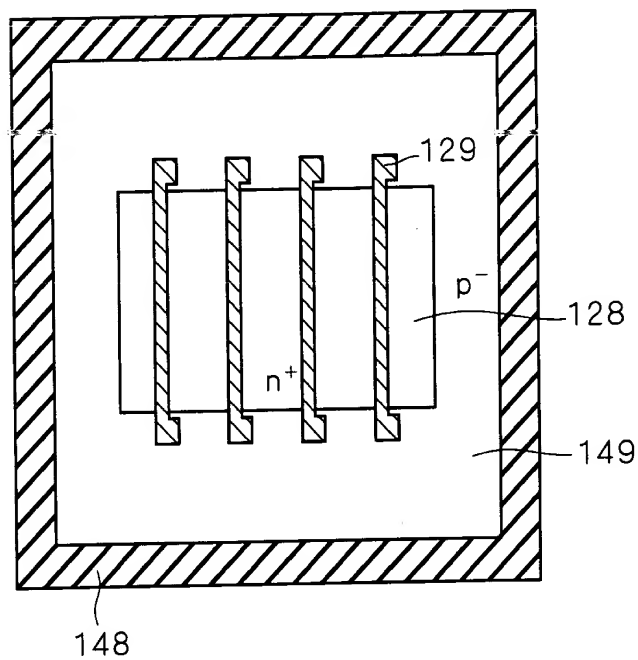


FIG. 77

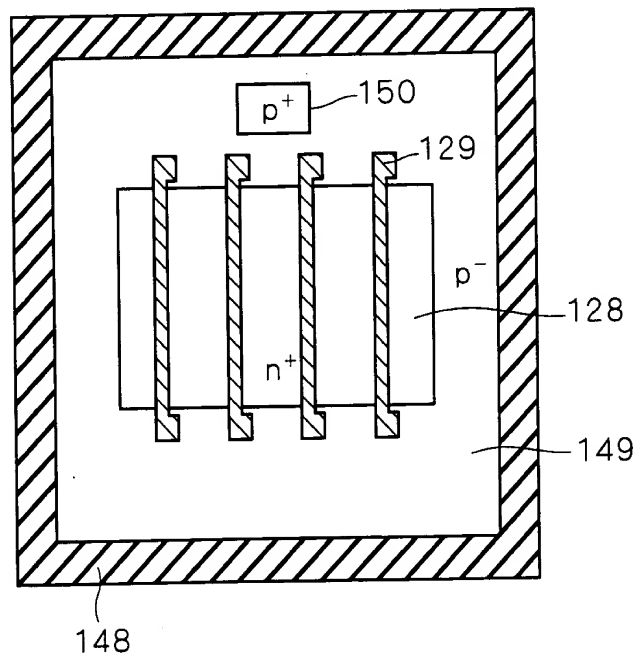


FIG. 78

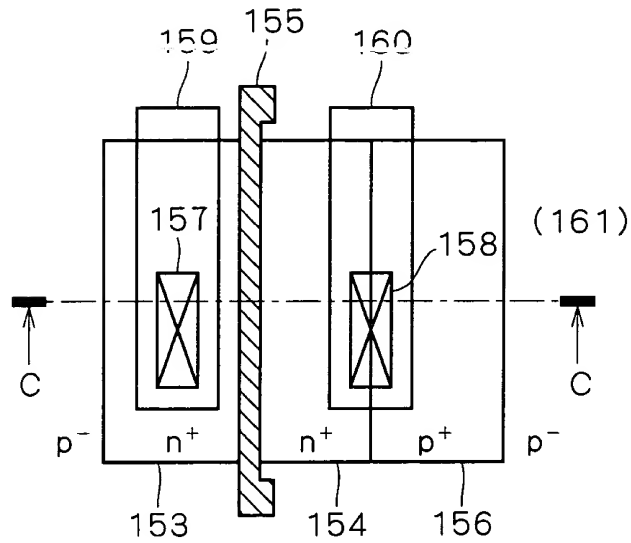


FIG. 79

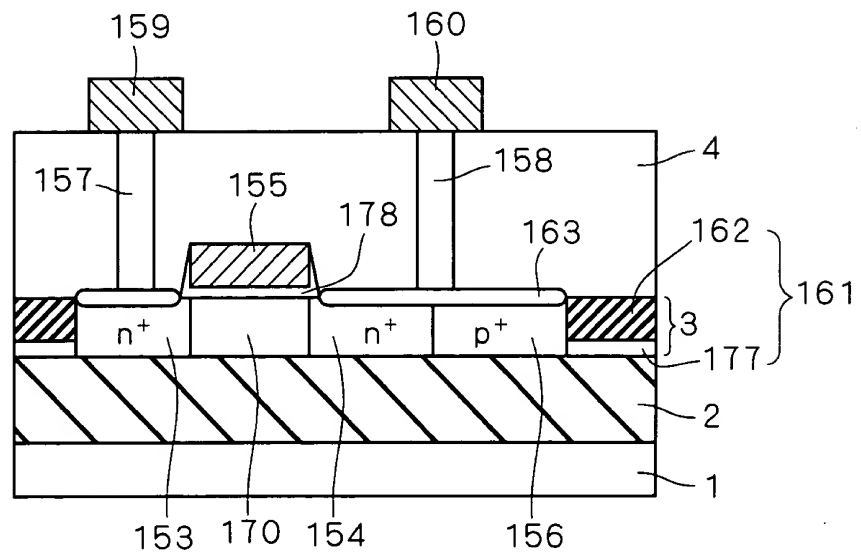


FIG. 80

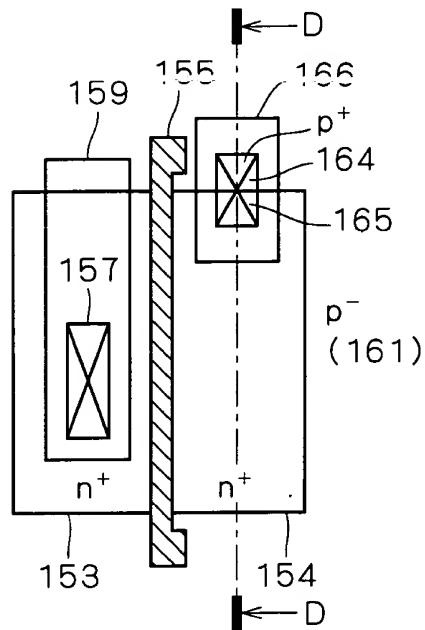


FIG. 81

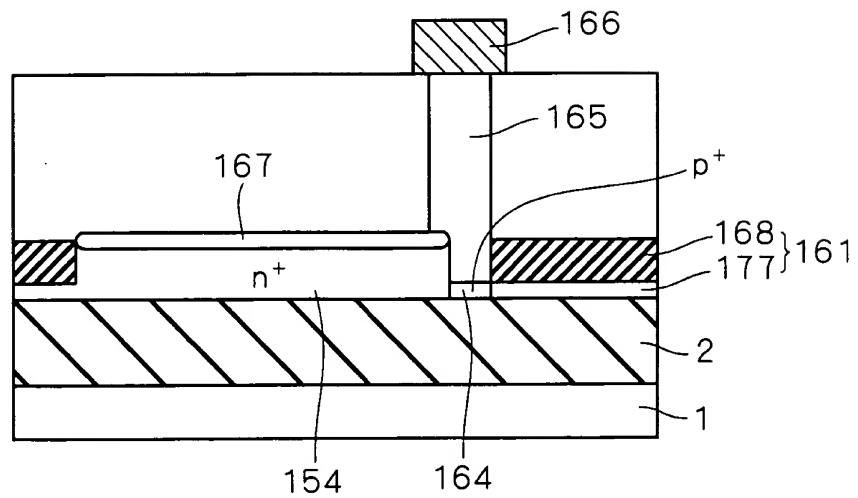


FIG. 82

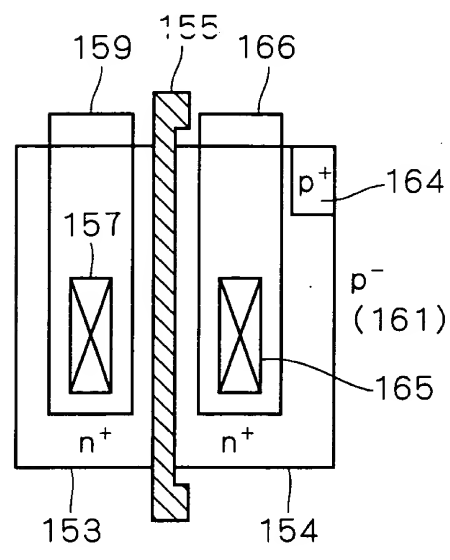


FIG. 83

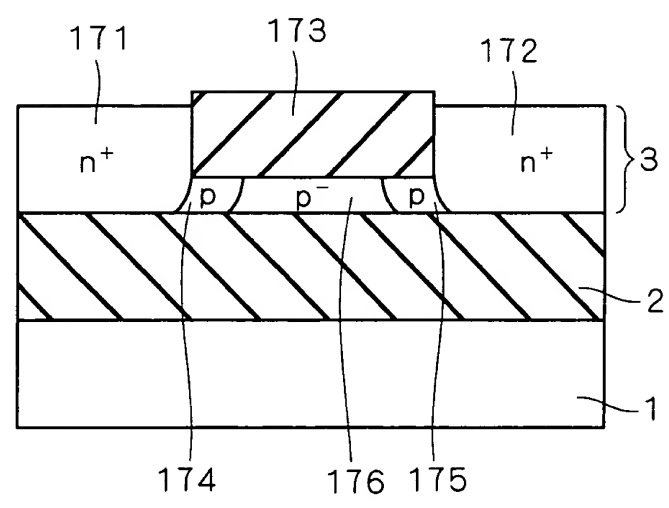


FIG. 84

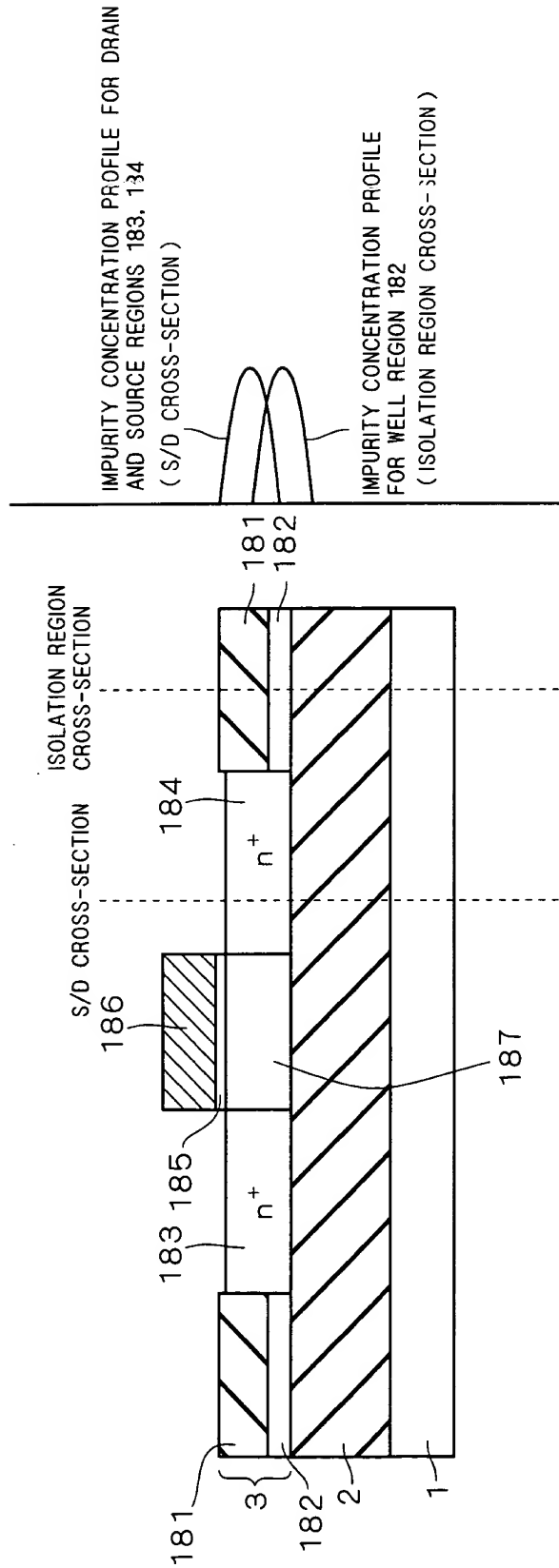


FIG. 86

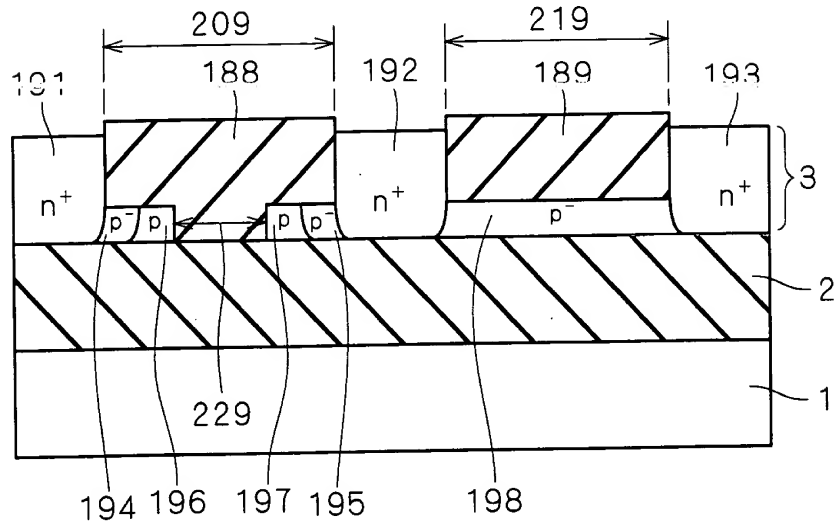


FIG. 87

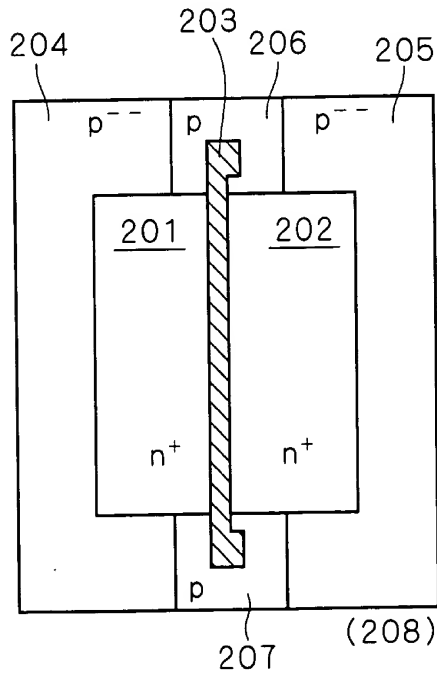


FIG. 88

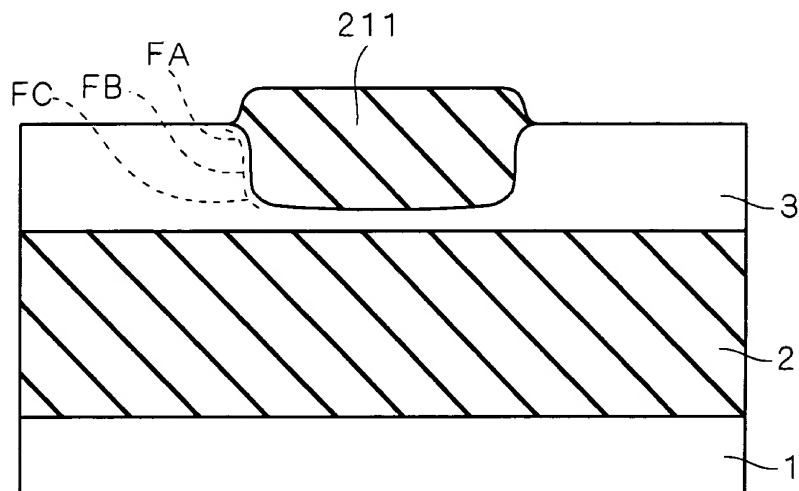
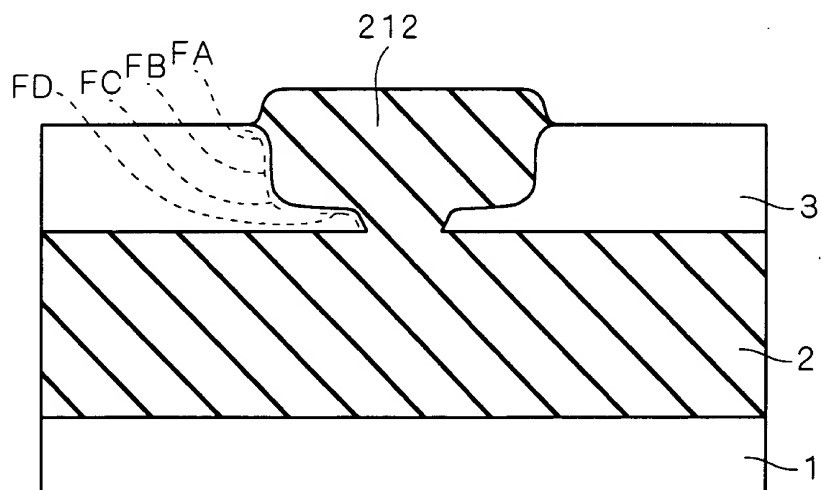
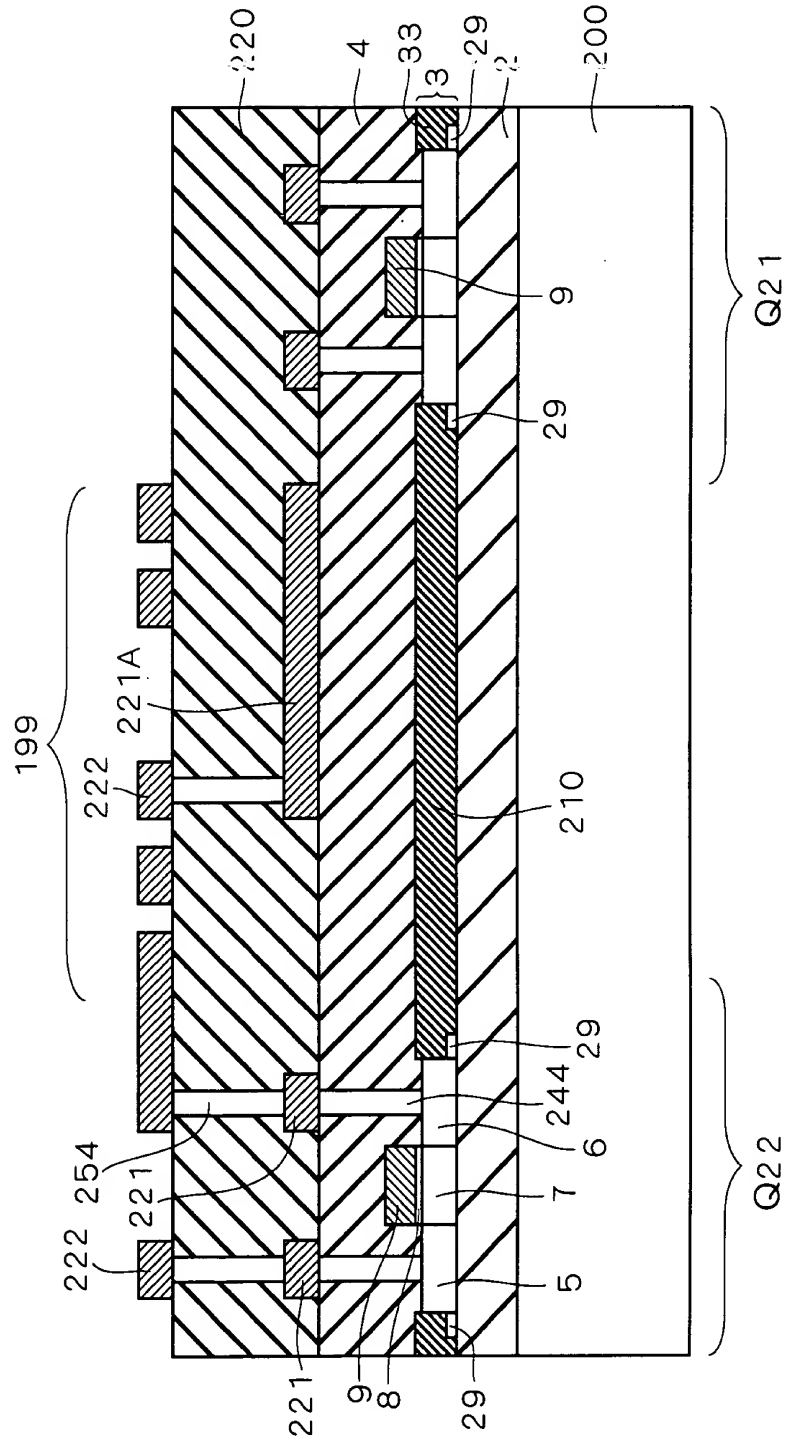


FIG. 89



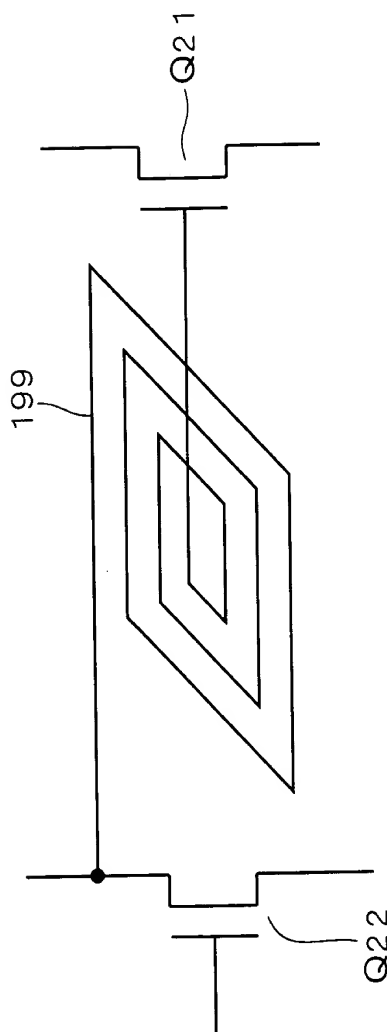
Sheet 4699460

FIG. 90



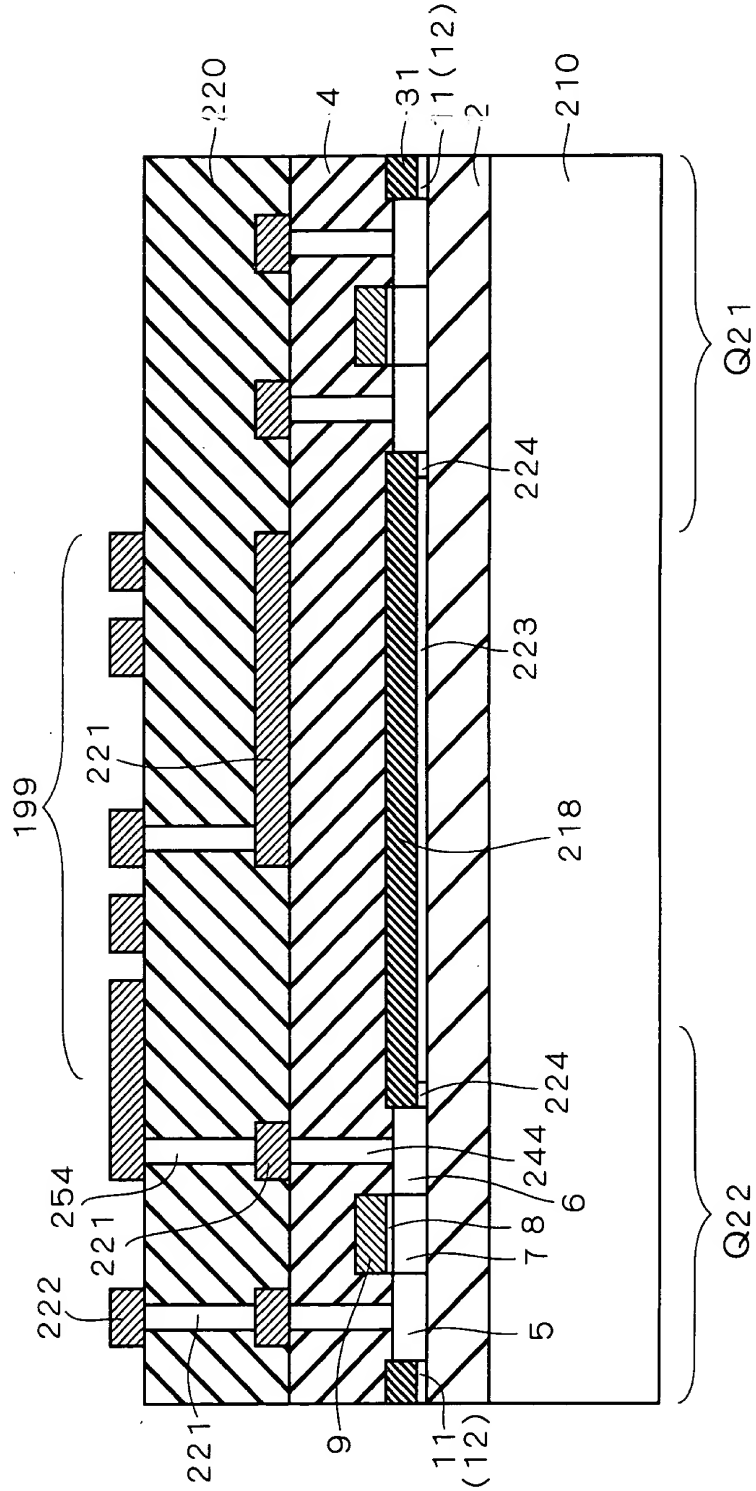
662247463463

FIG. 91



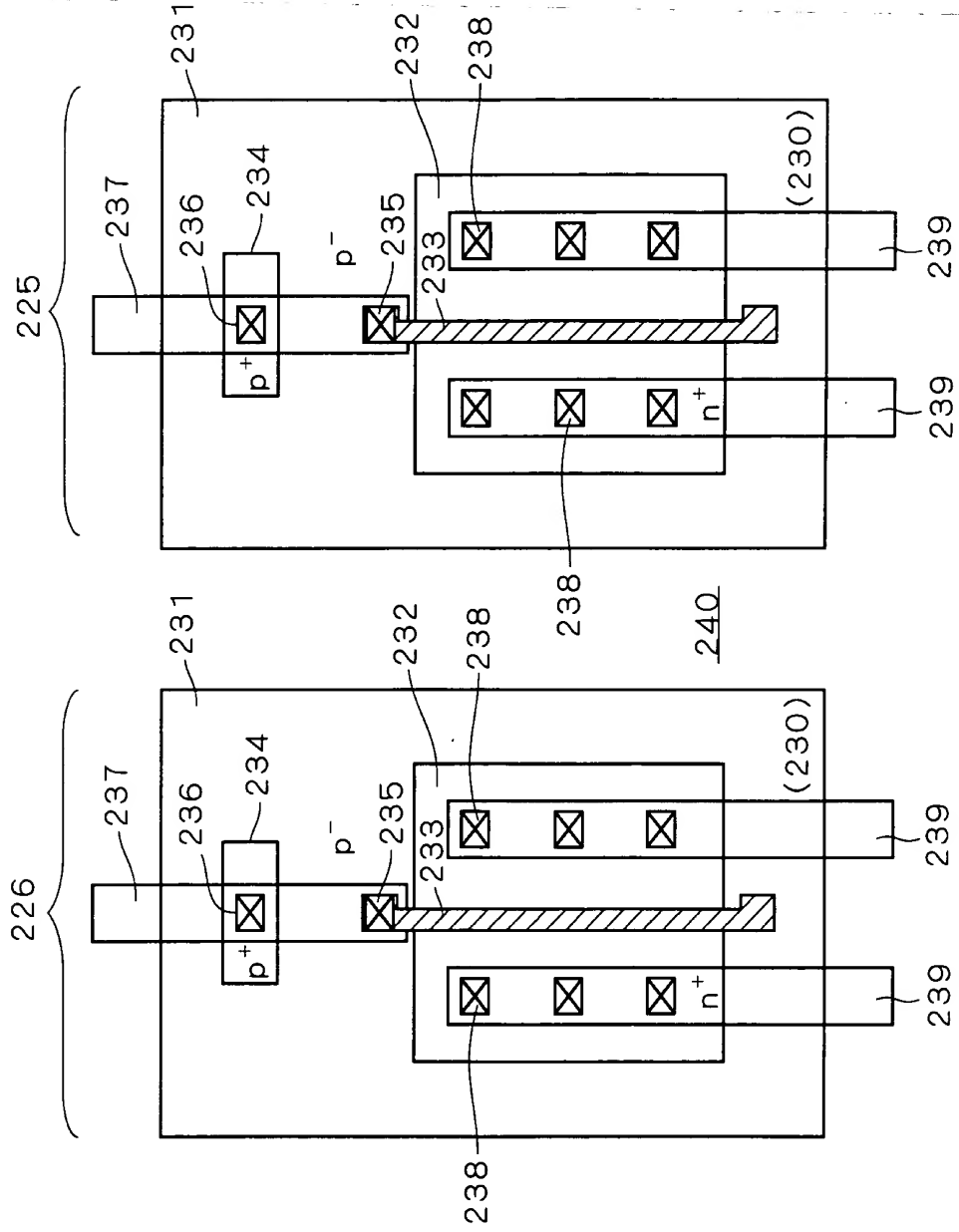
660227-4E693460

FIG. 92



Sheet 53 of 53

FIG. 93



DOCKET # 4269460

FIG. 94

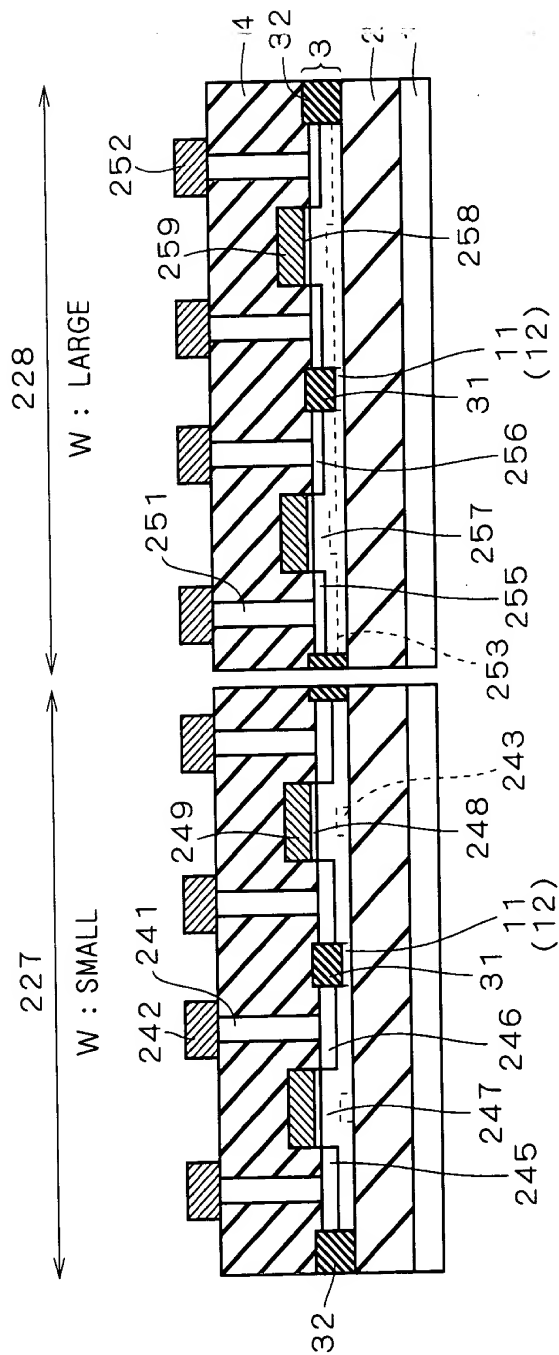


FIG. 95

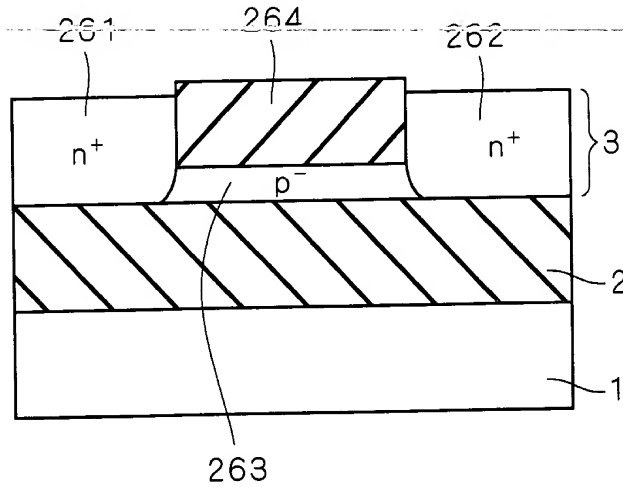


FIG. 96

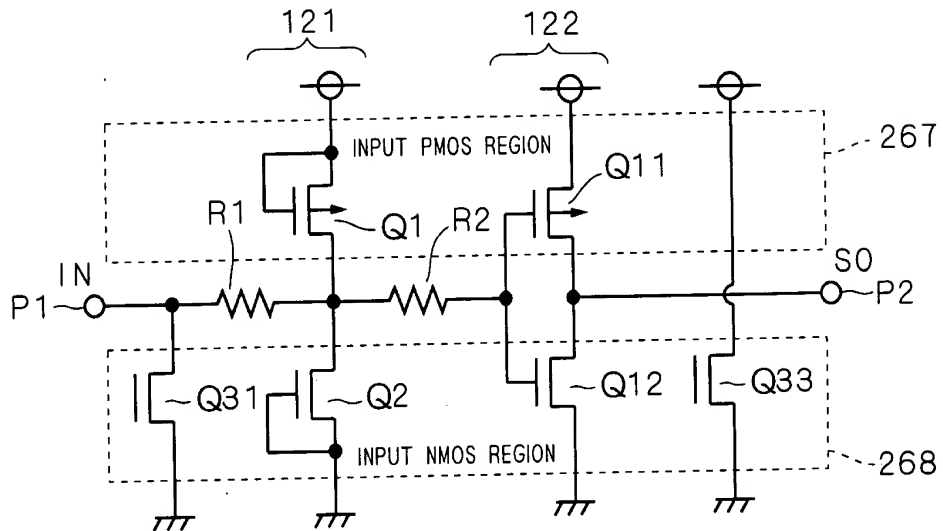


FIG. 97

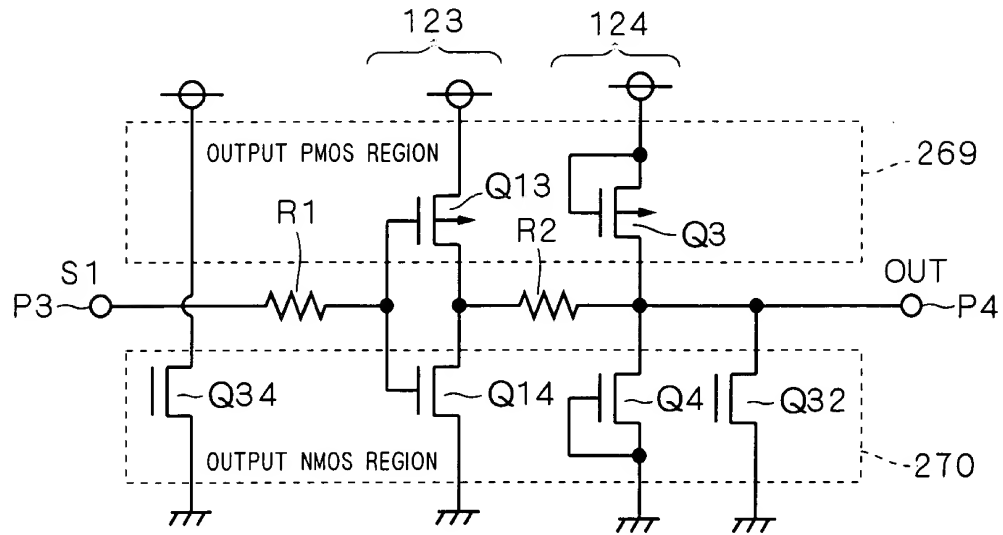


FIG. 98

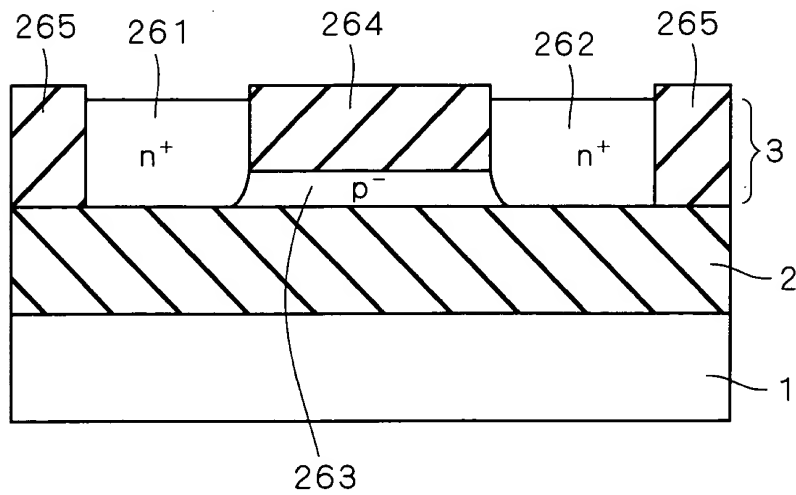


FIG. 99

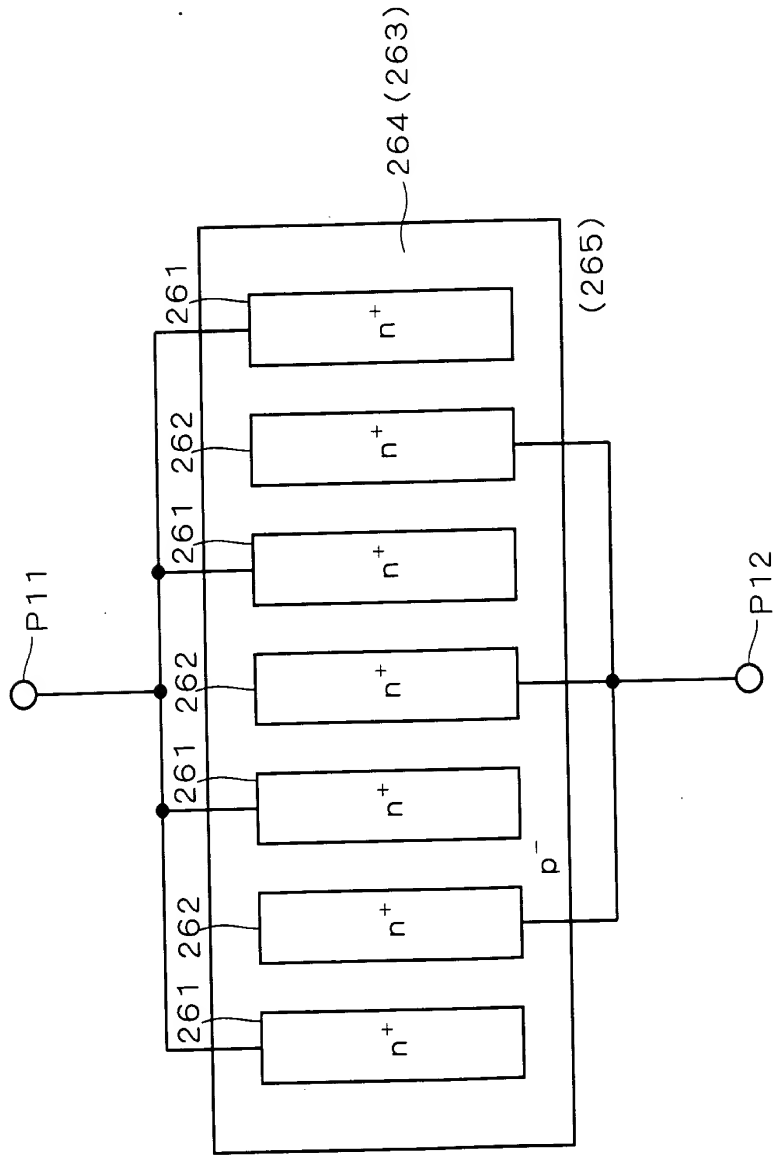


FIG. 100

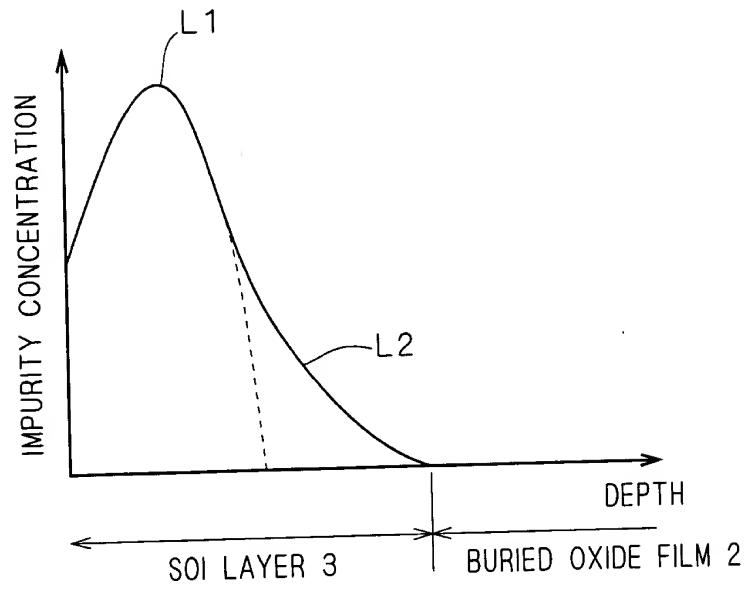
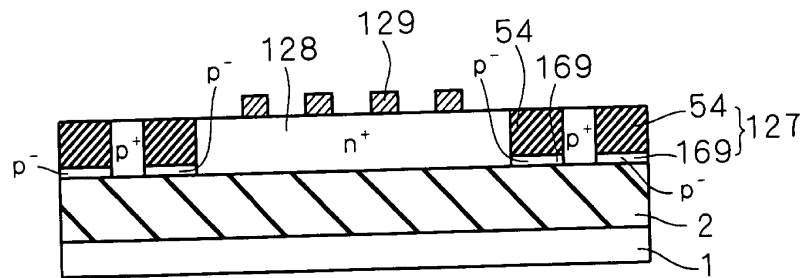


FIG. 101



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FIG. 102

